

Supplementary Materials

Synthesis and Functionalization of a 1,2-Bis(trimethylsilyl)-1,2-disilacyclohexene That Can Serve as a Unit of *cis*-1,2-Dialkyldisilene

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Contents

1. NMR Spectra.....	S2
2. UV-vis Spectra	S25
3. DFT Calculations	S30
Calculated Transition Energies and Oscillator Strengths of the Electron Transitions	S31
4. References	S48

1. NMR Spectra

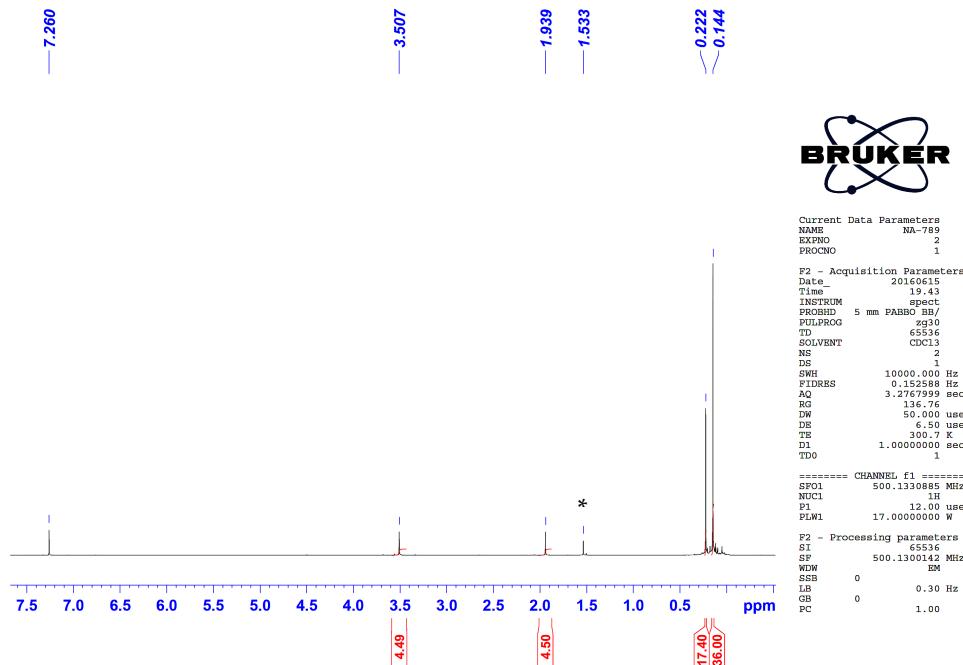


Figure S1. ^1H NMR spectrum of **2** in CDCl_3 at rt. * = H_2O .

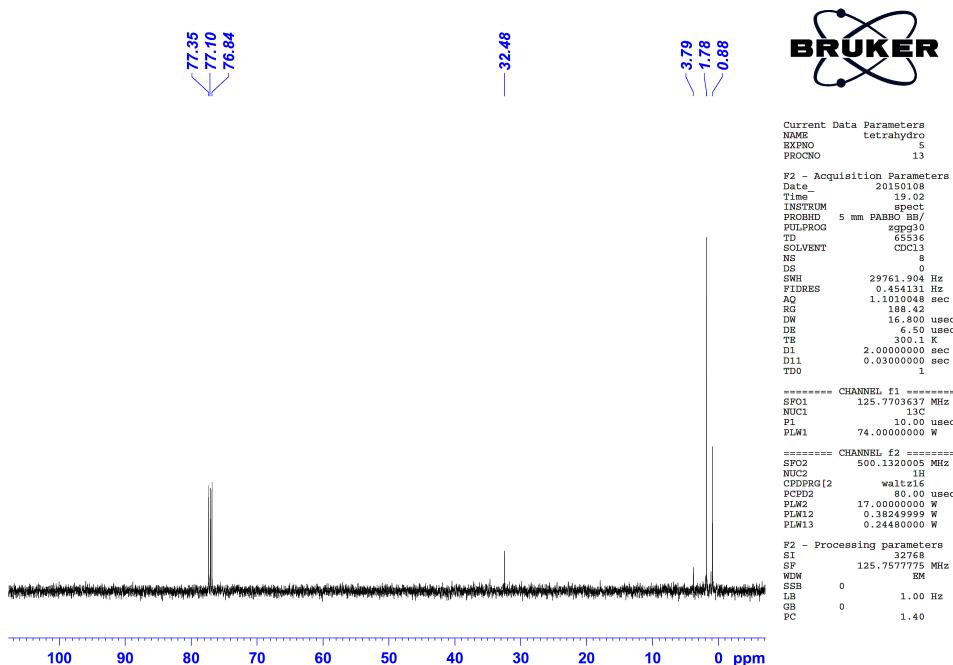


Figure S2. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **2** in CDCl_3 at rt.

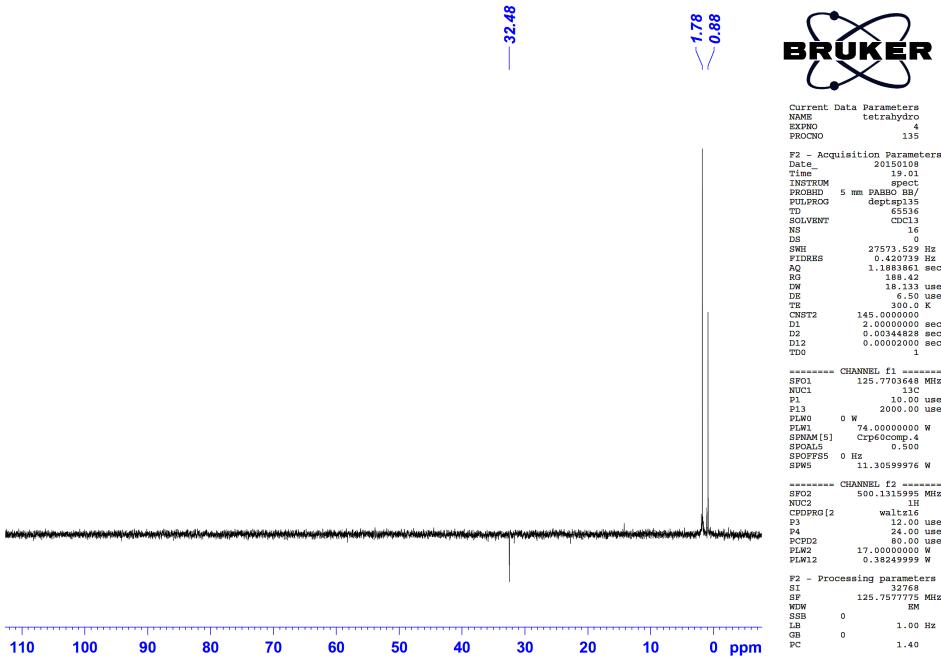


Figure S3. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **2** using DEPT 135 pulse sequence in CDCl_3 at rt.

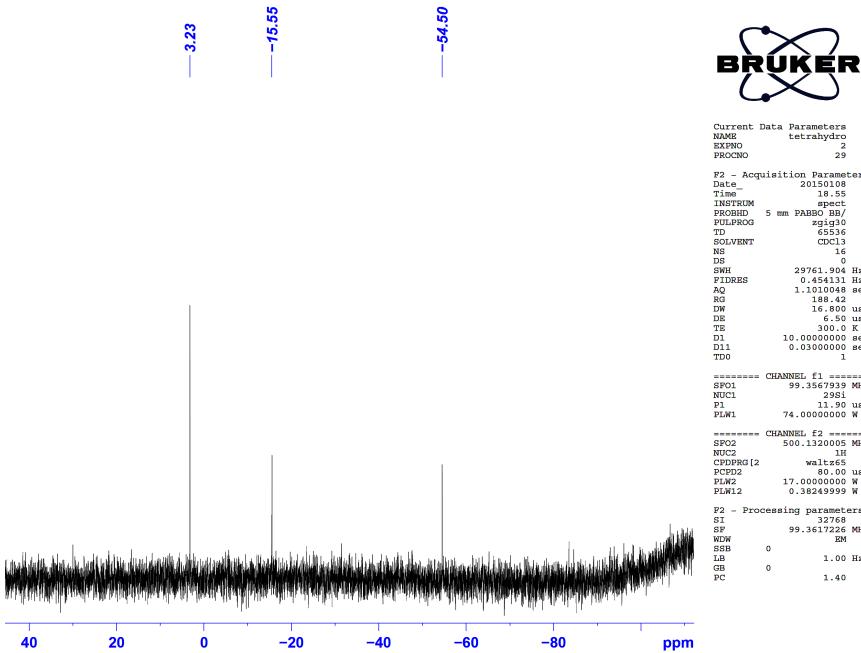


Figure S4. $^{29}\text{Si}\{^1\text{H}\}$ NMR spectrum of **2** using the inverse-gated pulse sequence in CDCl_3 at rt.

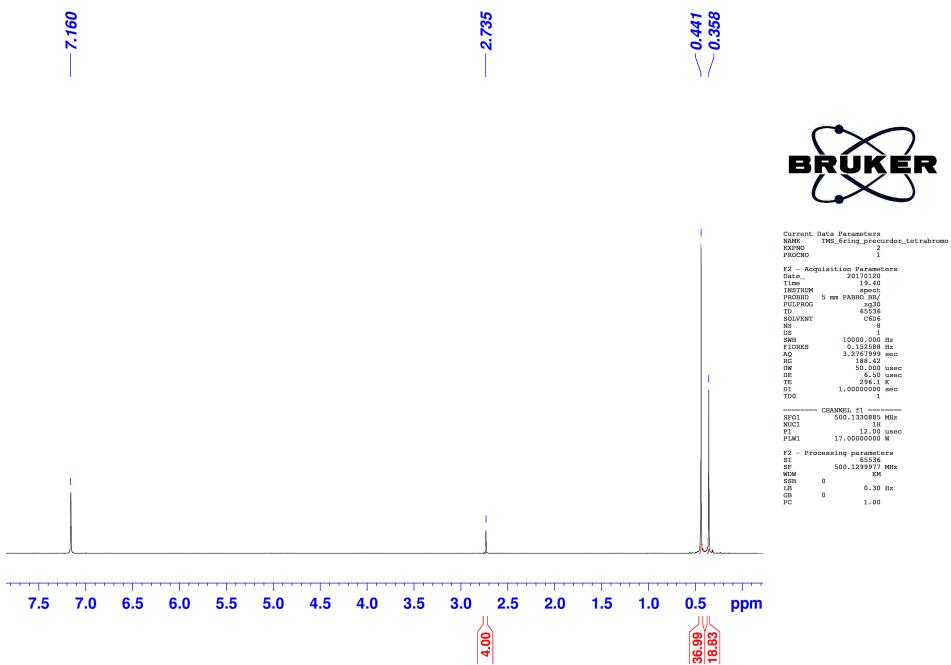


Figure S5. ^1H NMR spectrum of **3** in C_6D_6 at rt.

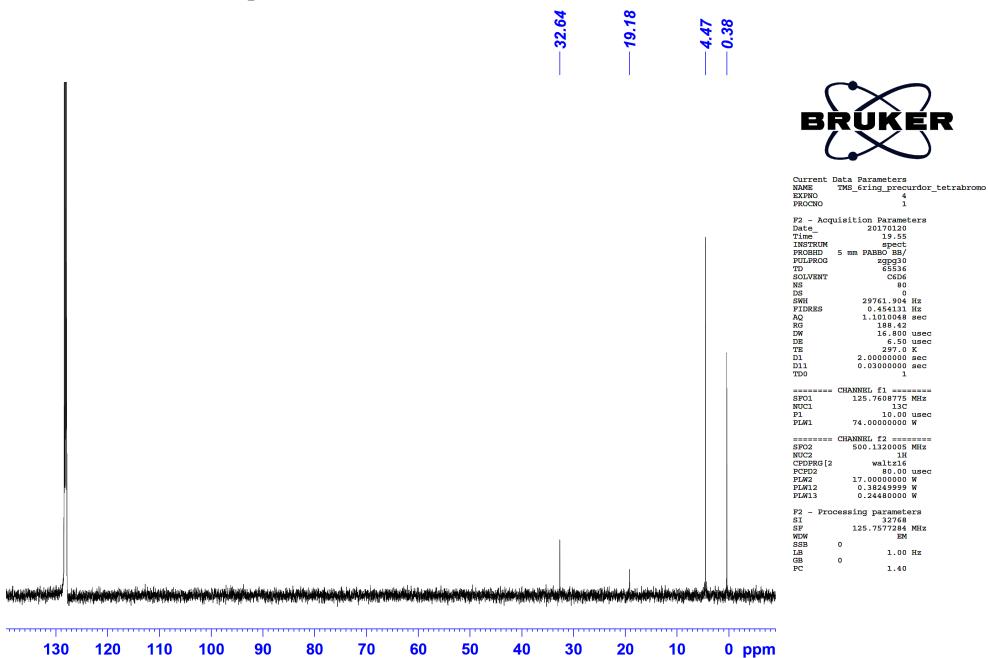


Figure S6. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **3** in C_6D_6 at rt.

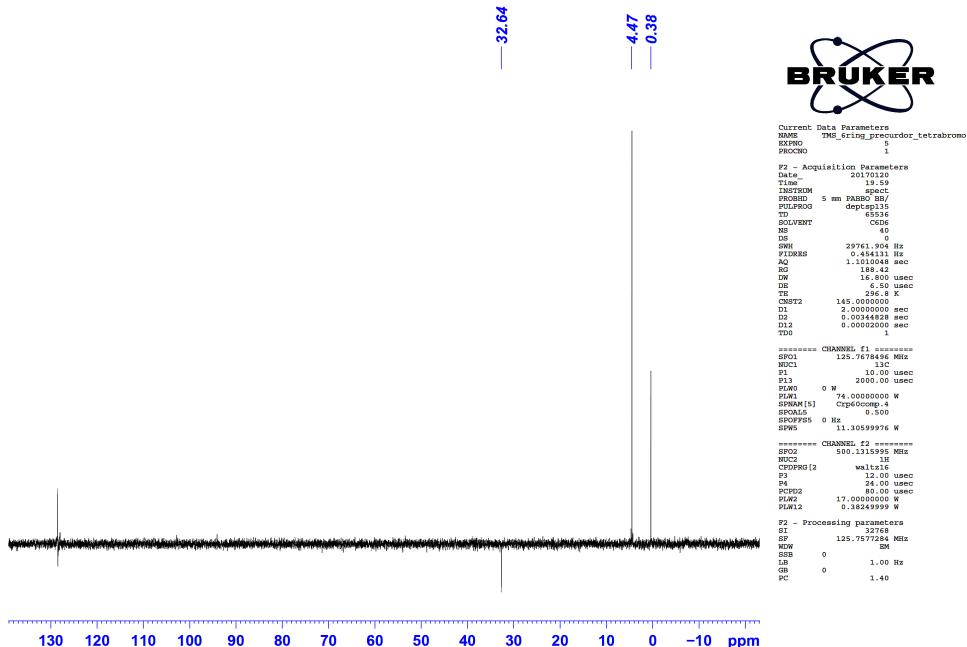


Figure S7. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **3** using DEPT 135 pulse sequence in C_6D_6 at rt.

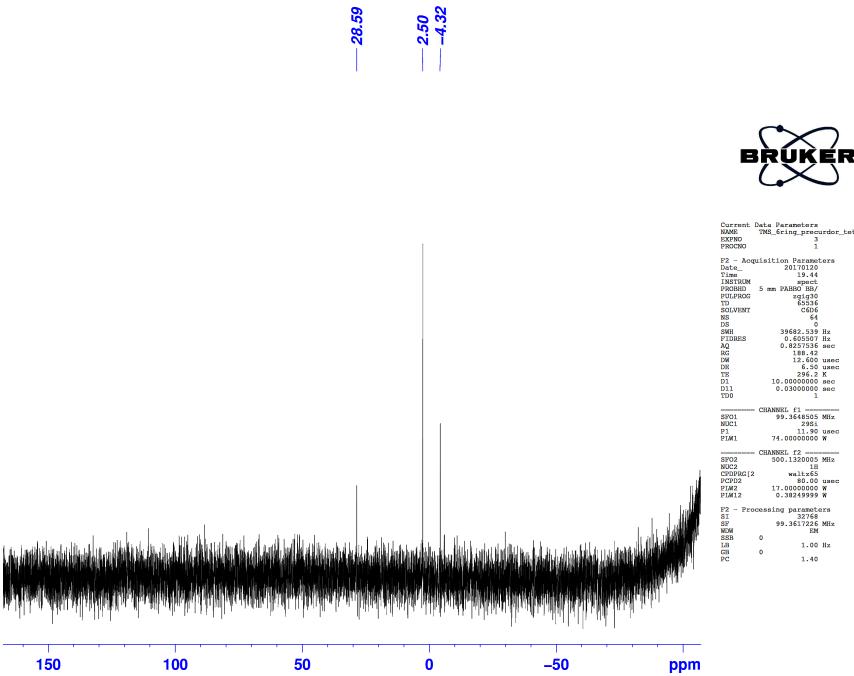


Figure S8. $^{29}\text{Si}\{^1\text{H}\}$ NMR spectrum of **3** using the inverse-gated pulse sequence in C_6D_6 at rt.

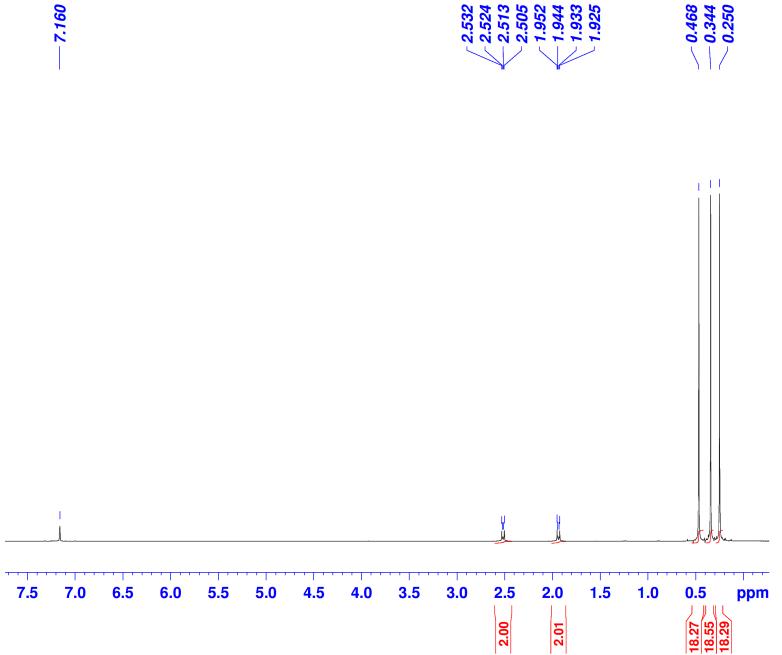


Figure S9. ^1H NMR spectrum of **1** in C_6D_6 at rt.

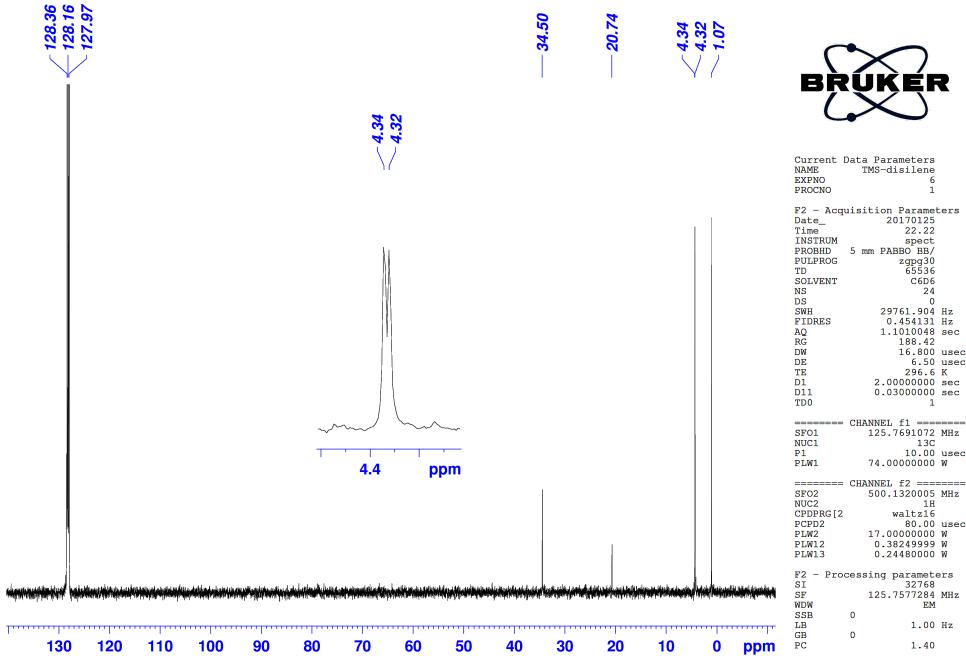


Figure S10. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **1** in C_6D_6 at rt.

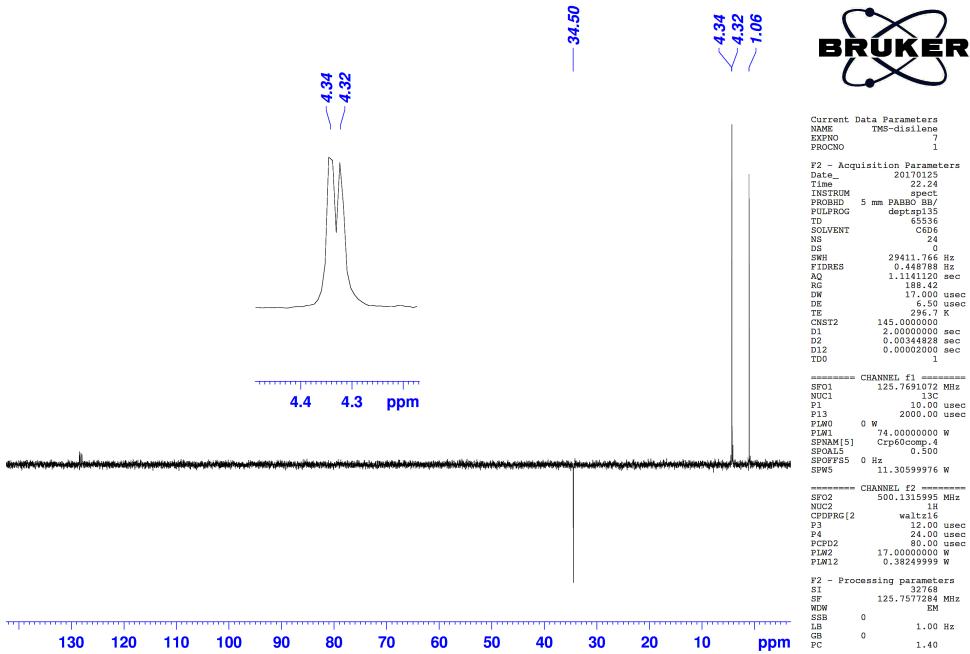


Figure S11. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **1** using DEPT 135 pulse sequence in C_6D_6 at rt.

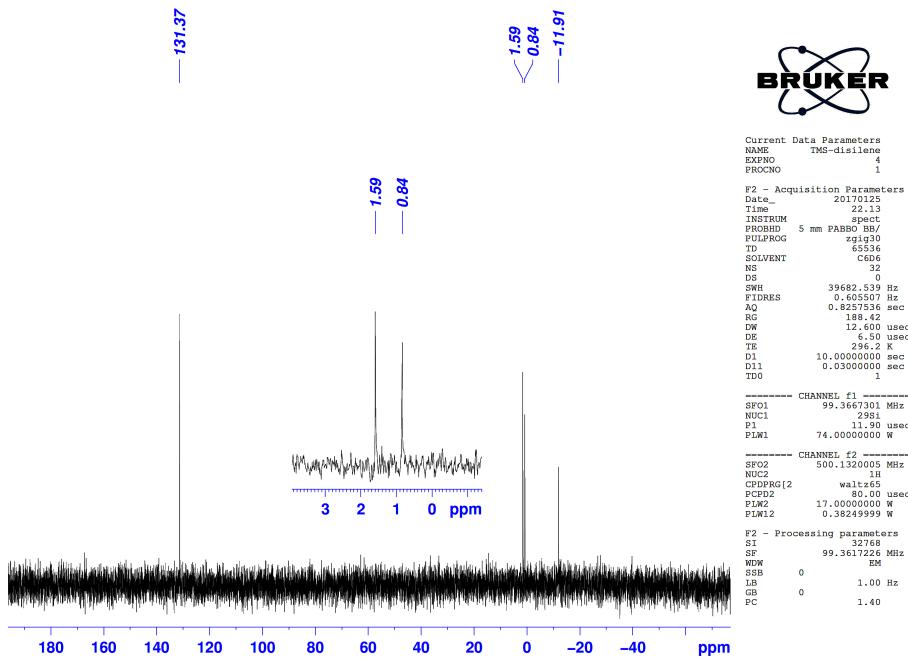


Figure S12. $^{29}\text{Si}\{\text{H}\}$ NMR spectrum of **1** using the inverse-gated pulse sequence in C_6D_6 at rt.

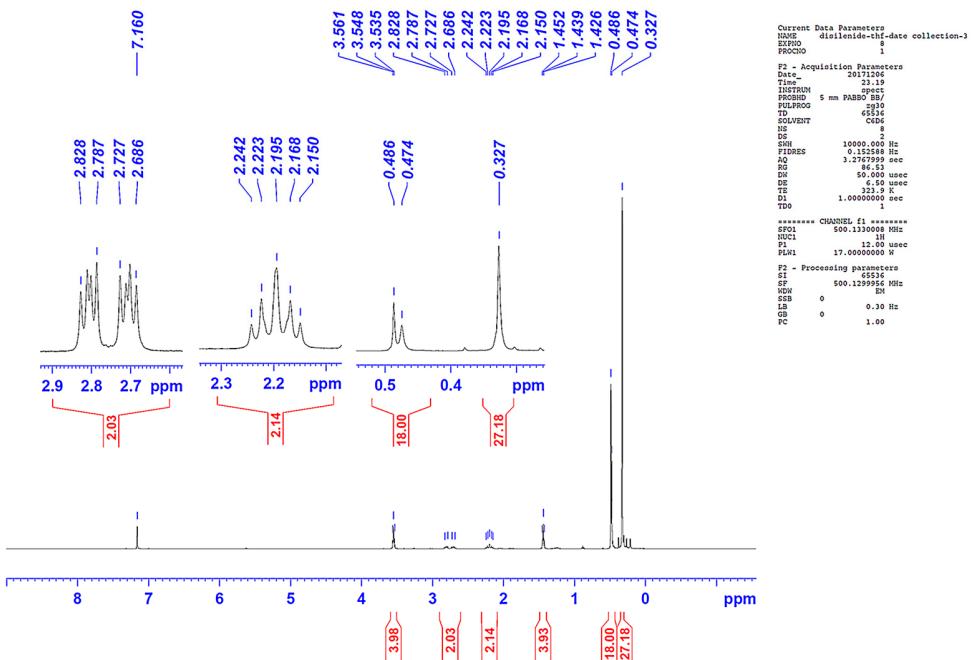


Figure S13. ^1H NMR spectrum of $[\text{K}(\text{thf})]4$ in C_6D_6 at 50°C .

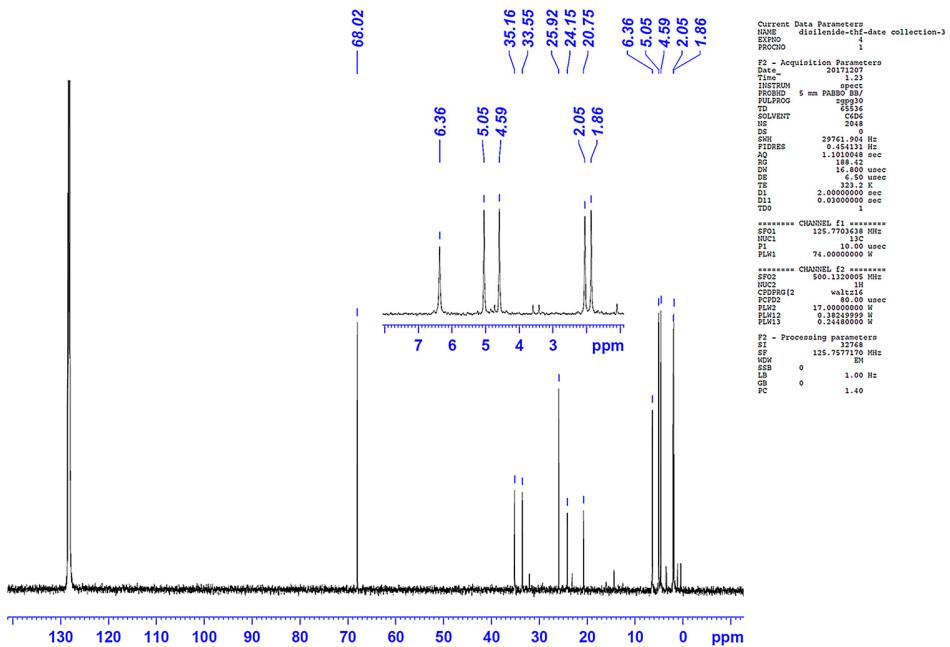


Figure S14. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of $[\text{K}(\text{thf})]4$ in C_6D_6 at 50°C .

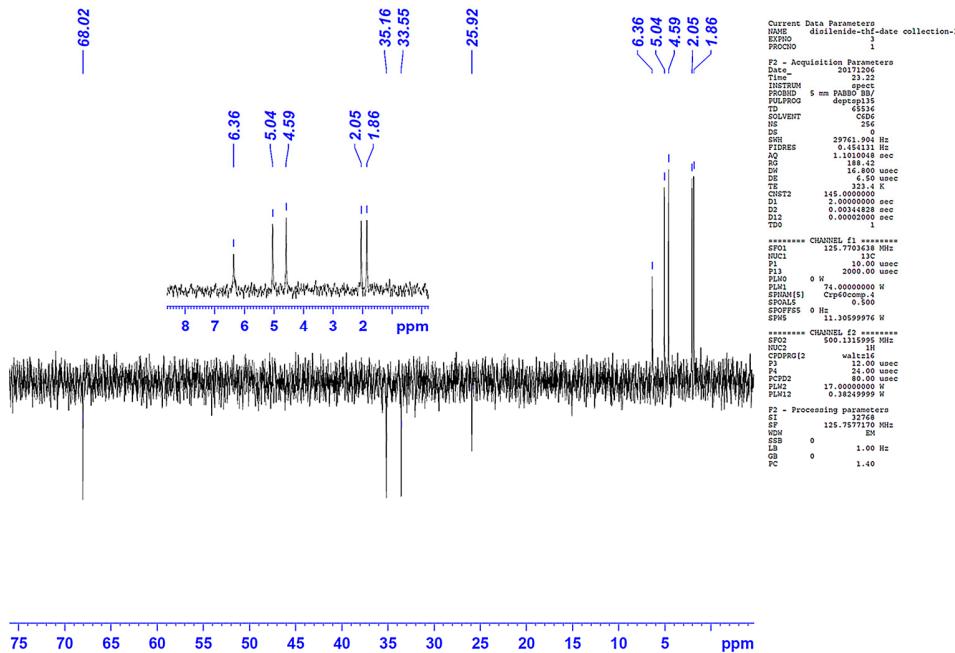


Figure S15. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of $[\text{K}(\text{thf})]4$ using DEPT 135 pulse sequence in C_6D_6 at 50 °C.

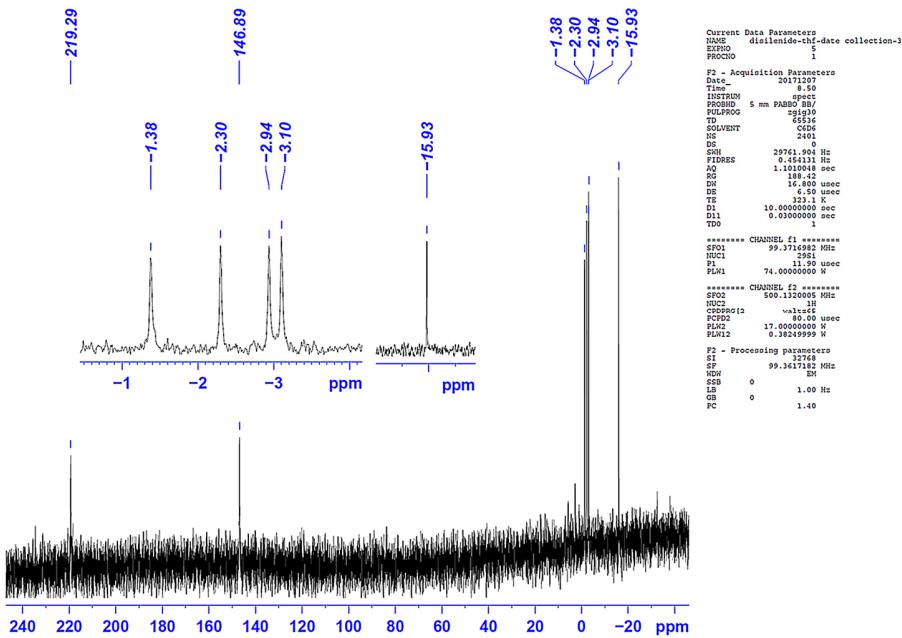


Figure S16. $^{29}\text{Si}\{\text{H}\}$ NMR spectrum of $[\text{K}(\text{thf})]4$ using the inverse-gated pulse sequence in C_6D_6 at 50 °C.

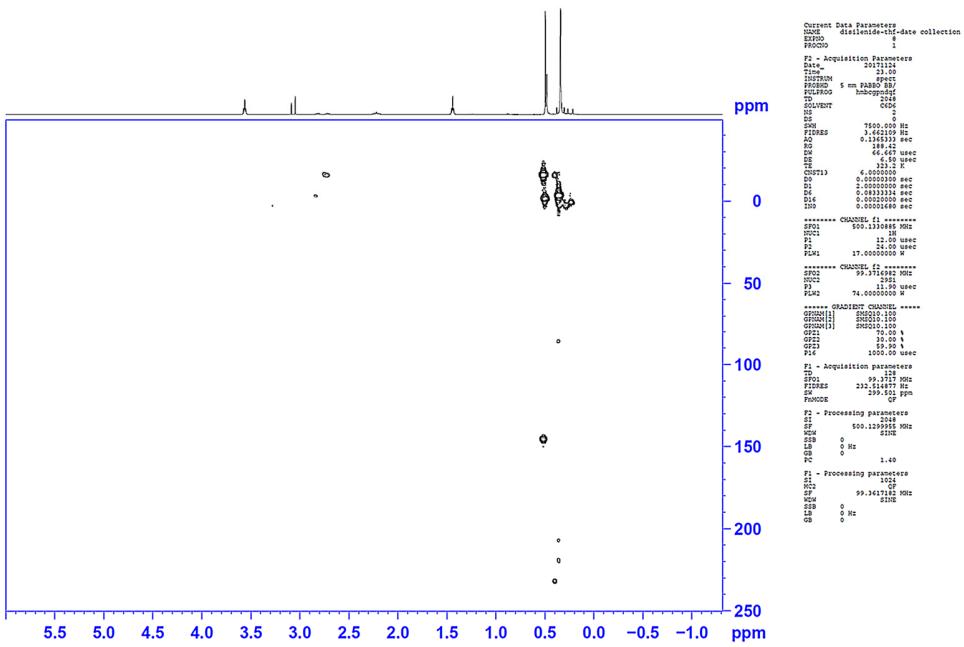


Figure S17. ^1H - ^{29}Si HMBC 2D NMR spectrum of $[\text{K}(\text{thf})]\text{4}$ in C_6D_6 at 50 °C.

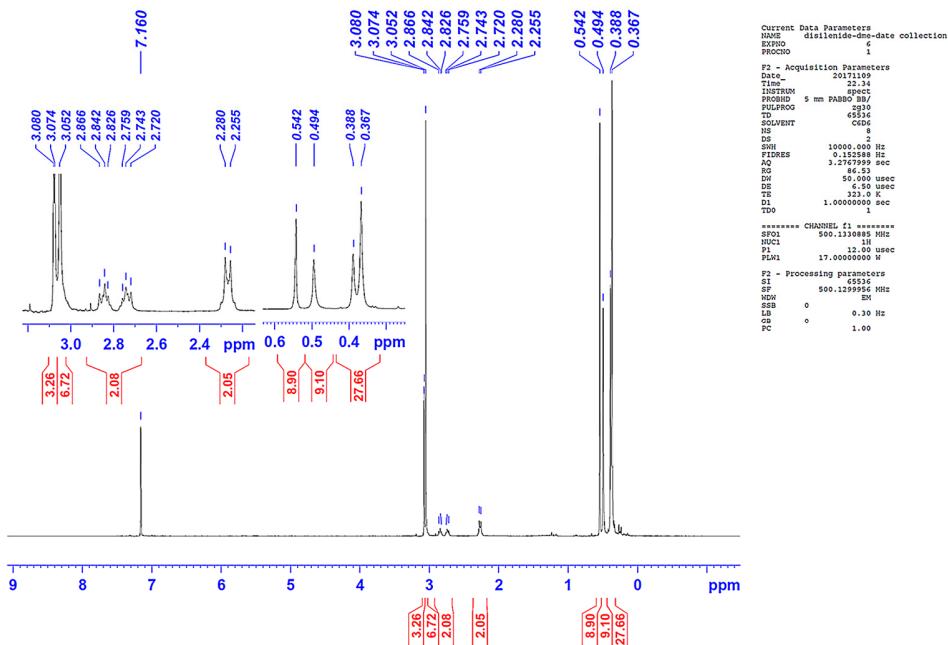


Figure S18. ^1H NMR spectrum of $[\text{K}(\text{dme})]\text{4}$ in C_6D_6 at 50 °C.

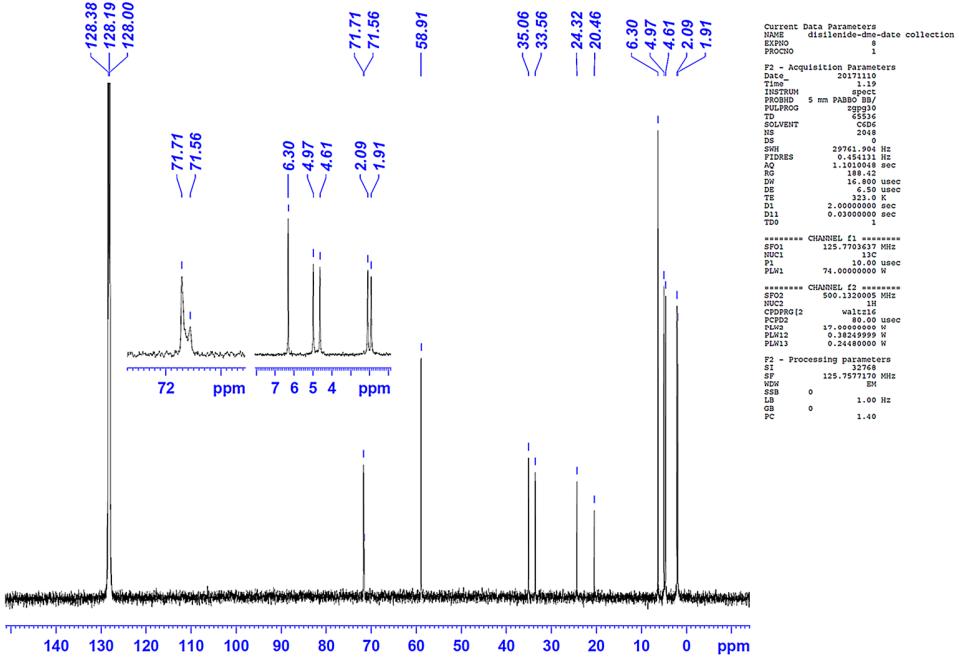


Figure S19. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of $[\text{K}(\text{dme})]\text{4}$ in C_6D_6 at 50°C .

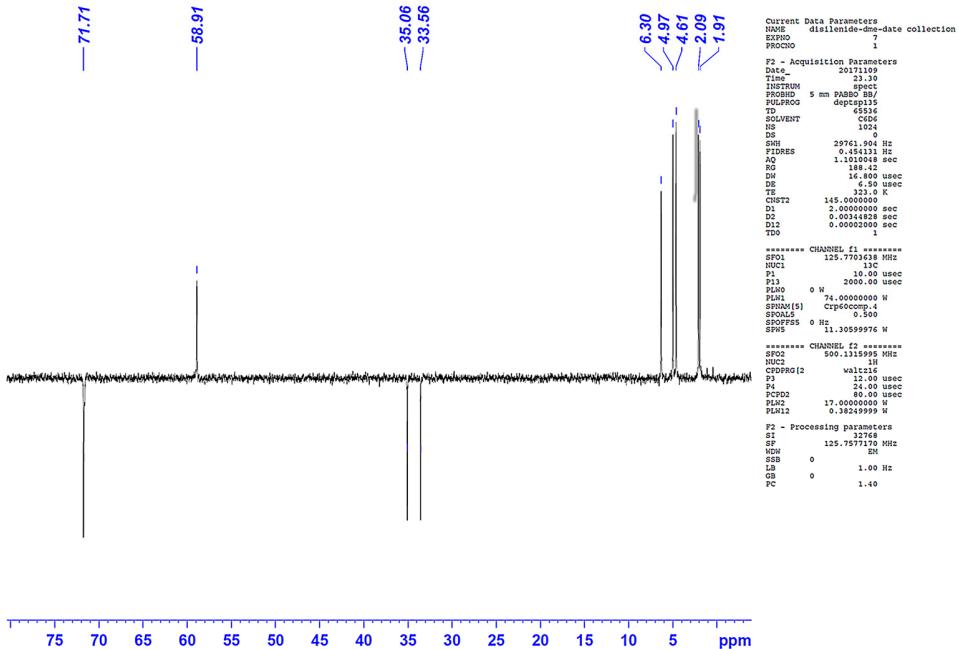


Figure S20. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of $[\text{K}(\text{dme})]\text{4}$ using DEPT 135 pulse sequence in C_6D_6 at 50°C .

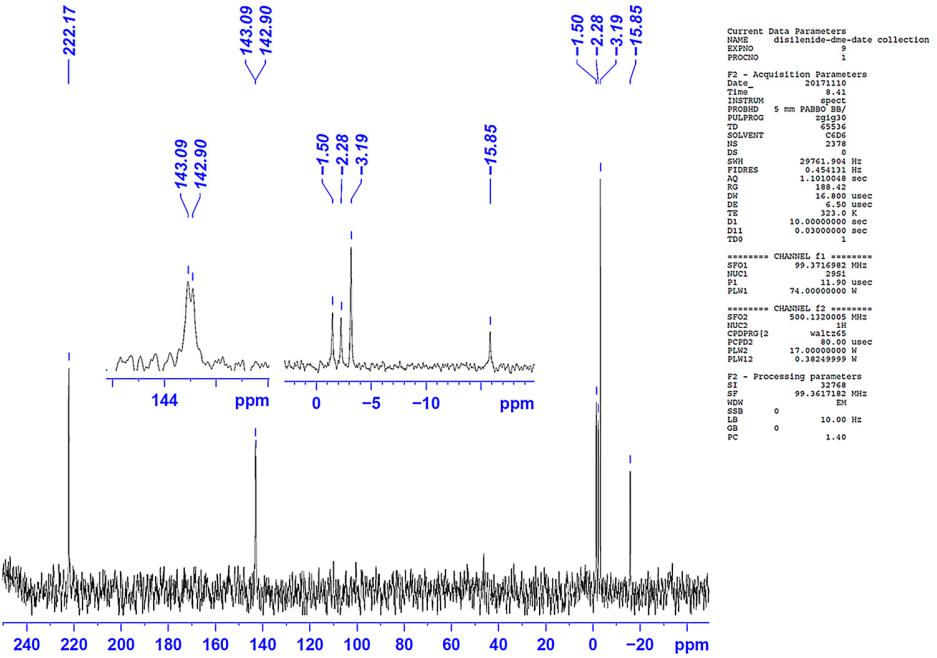


Figure S21. $^{29}\text{Si}\{\text{H}\}$ NMR spectrum of $[\text{K}(\text{dme})]4$ using the inverse-gated pulse sequence in C_6D_6 at 50°C .

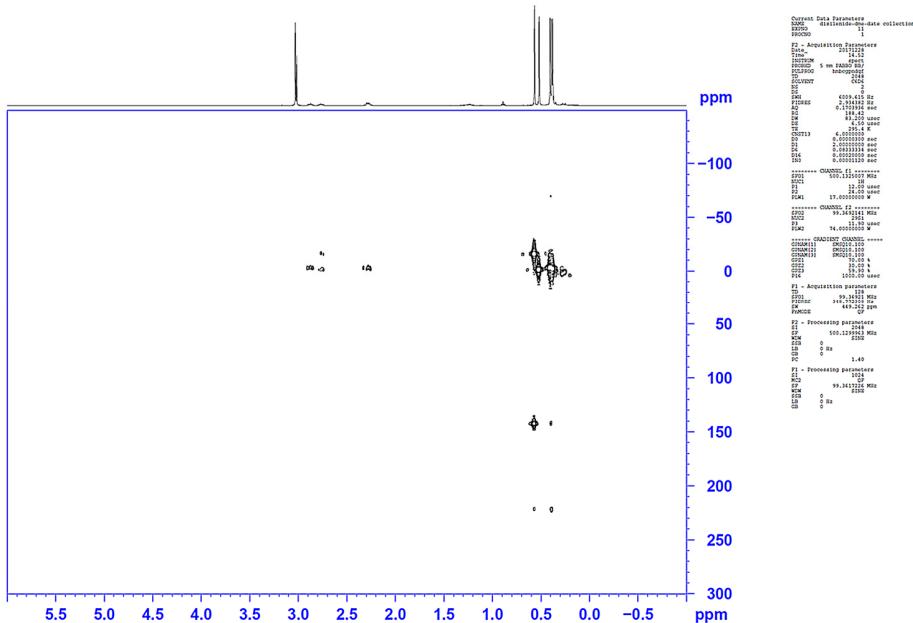


Figure S22. ^1H - ^{29}Si HMBC 2D NMR spectrum of $[\text{K}(\text{dme})]4$ in C_6D_6 at 50°C .

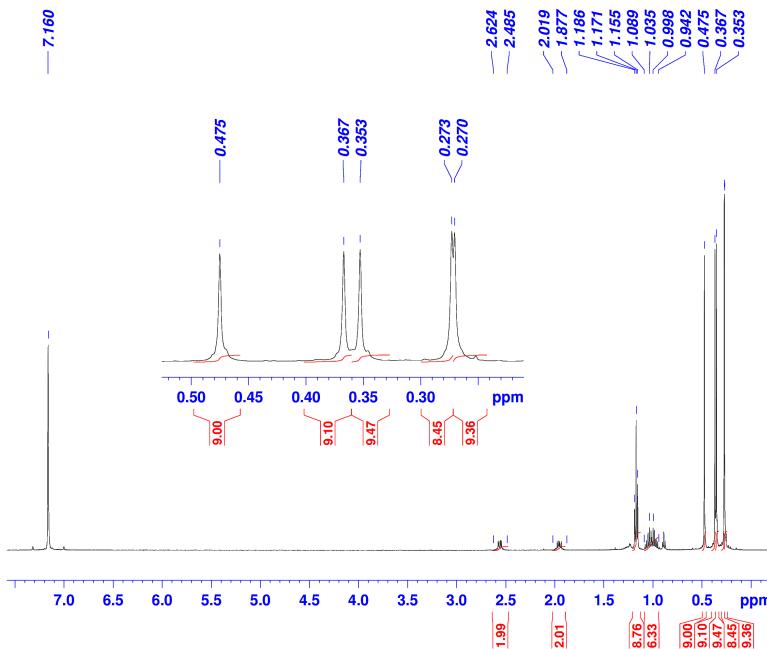


Figure S23. ^1H NMR spectrum of 5 in C_6D_6 at rt (* = hexane)

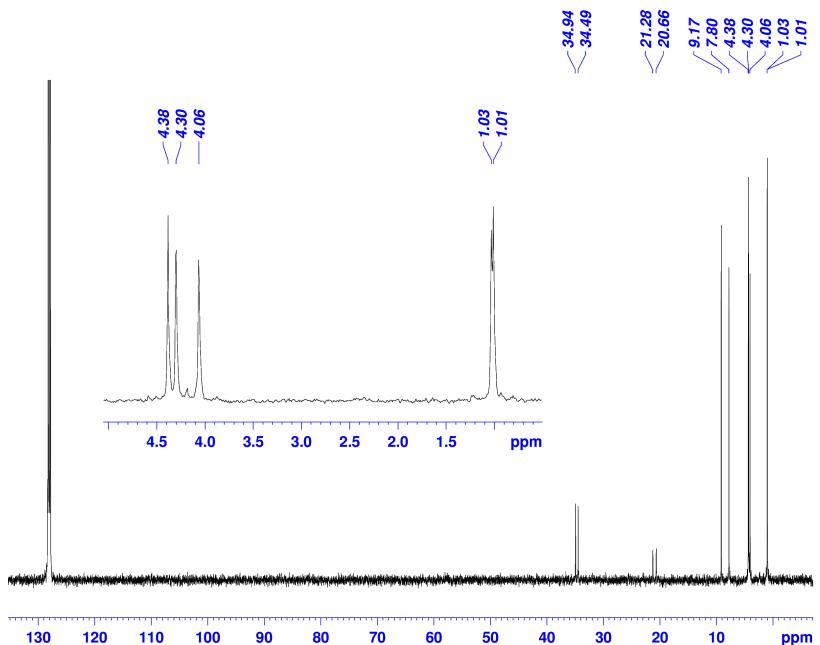


Figure S24. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of 5 in C_6D_6 at rt.

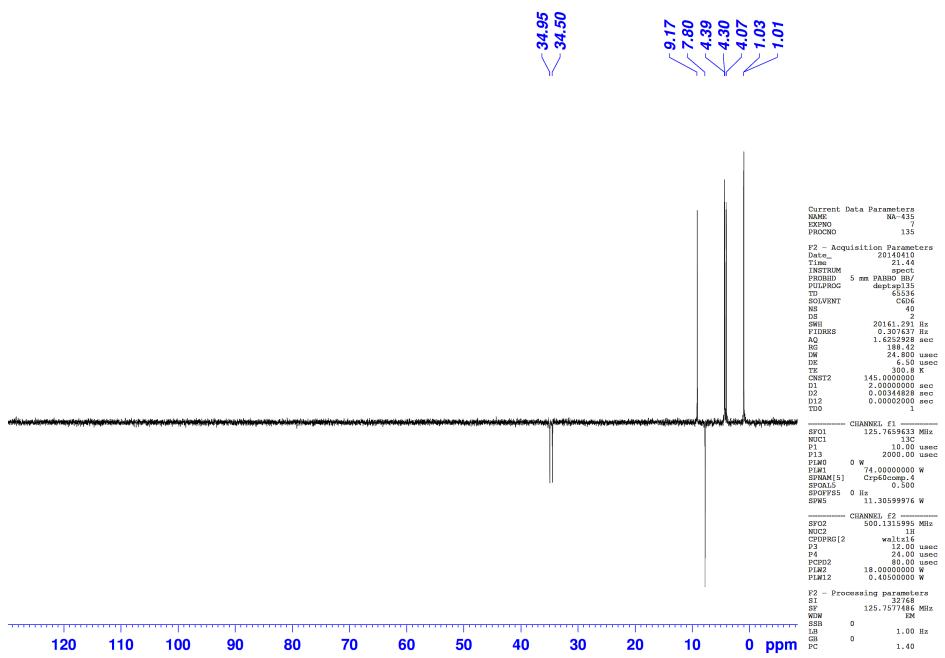


Figure S25. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **5** using DEPT 135 pulse sequence in C_6D_6 at rt.

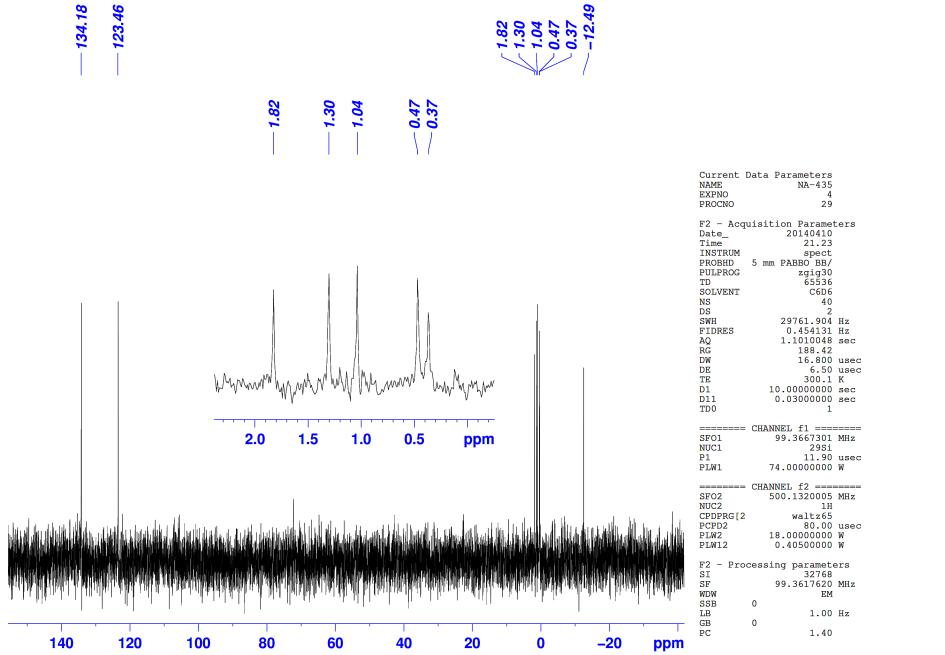


Figure S26. $^{29}\text{Si}\{^1\text{H}\}$ NMR spectrum of **5** using the inverse-gated pulse sequence in C_6D_6 at rt.

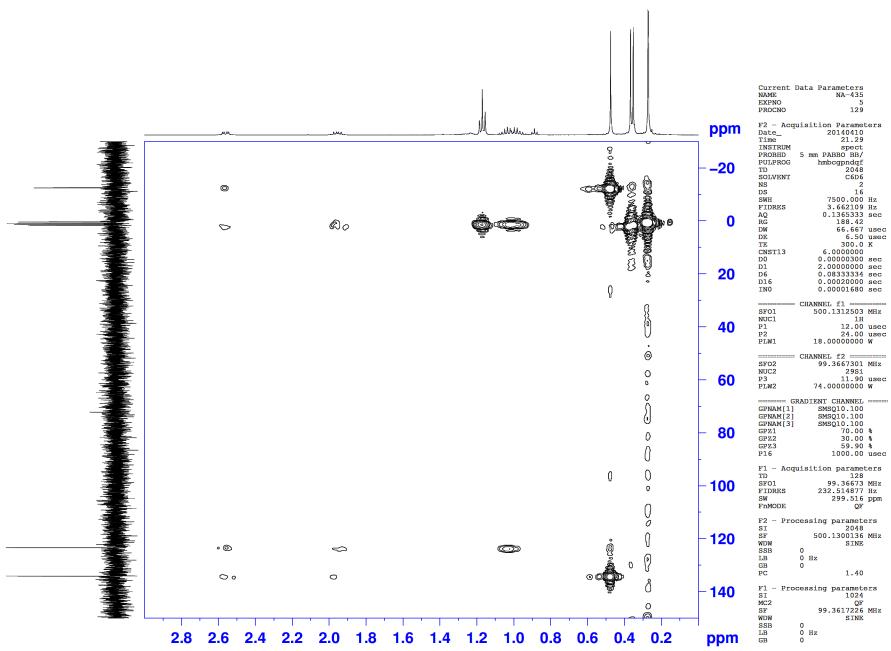


Figure S27. ^1H - ^{29}Si HMBC 2D NMR spectrum of **5** in C_6D_6 at rt.

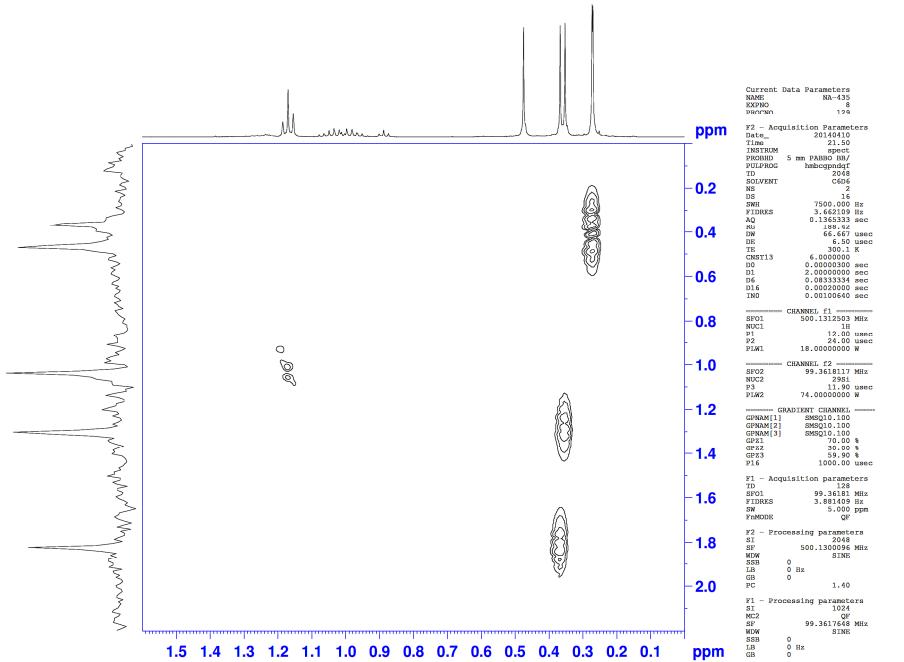


Figure S28. Magnified ^1H - ^{29}Si HMBC 2D NMR spectrum of **5** (SiMe₃ region) in C_6D_6 at rt.

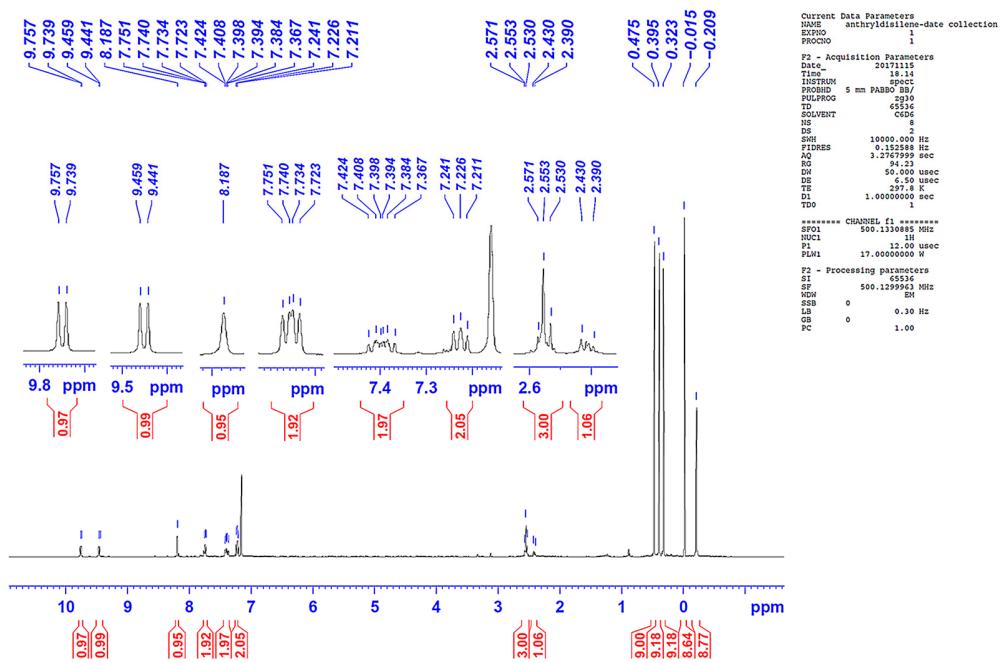


Figure S29. ^1H NMR spectrum of **6** in C_6D_6 at rt.

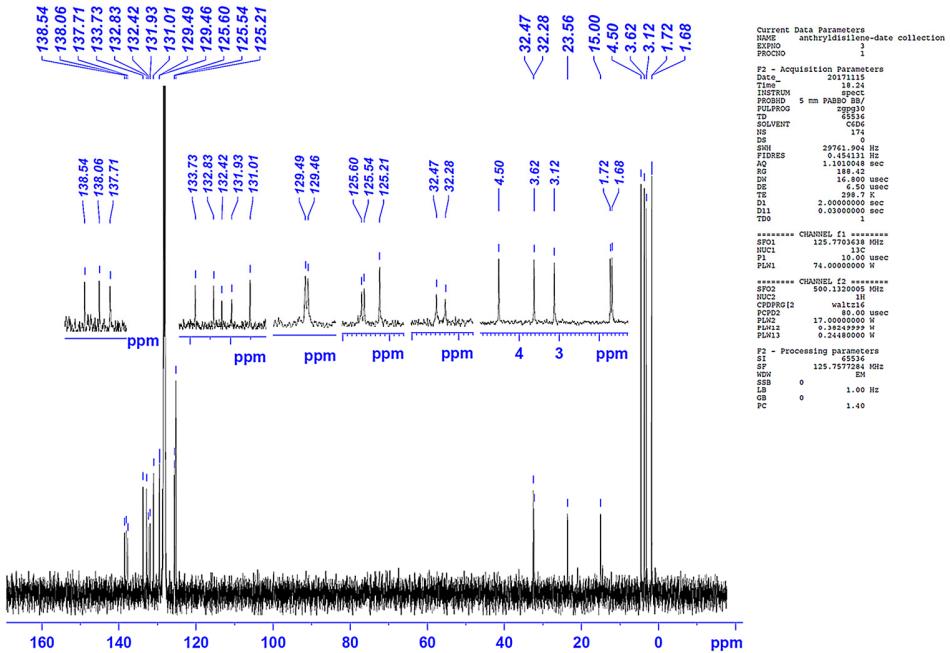


Figure S30. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **6** in C_6D_6 at rt.

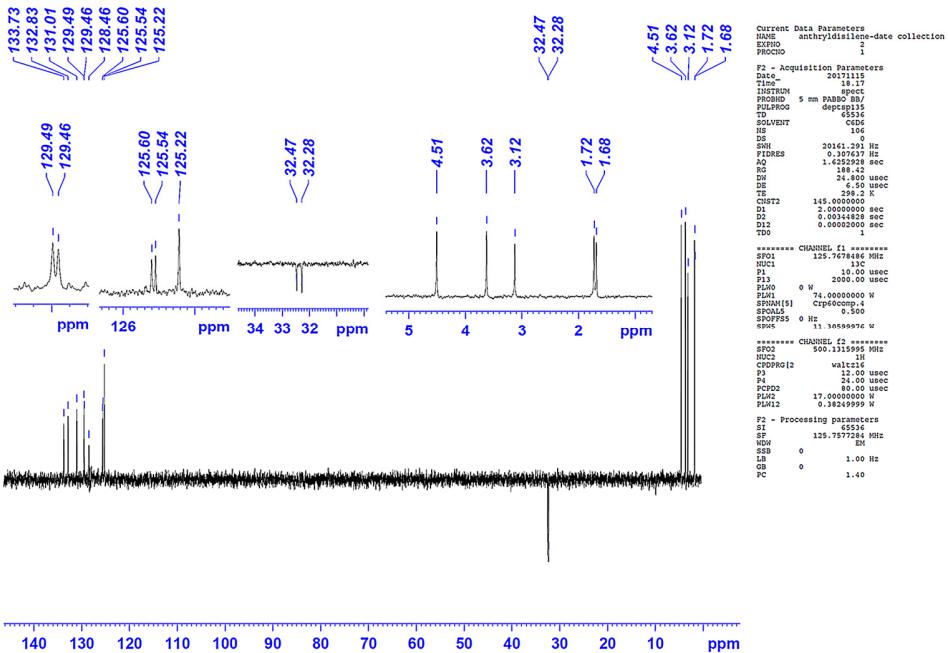


Figure S31. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **6** using DEPT 135 pulse sequence in C_6D_6 at rt.

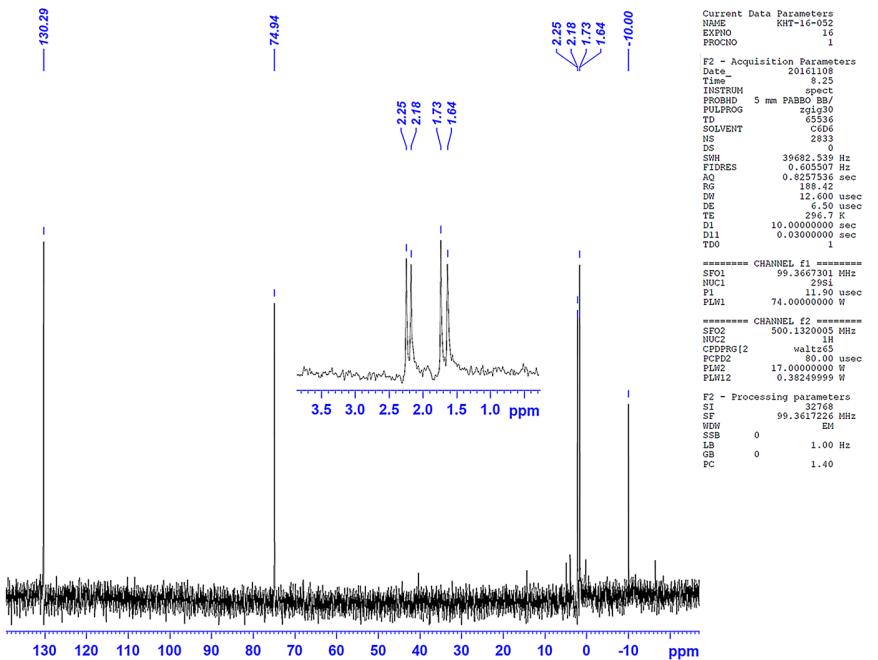


Figure S32. $^{29}\text{Si}\{\text{H}\}$ NMR spectrum of **6** using the inverse-gated pulse sequence in C_6D_6 at rt.

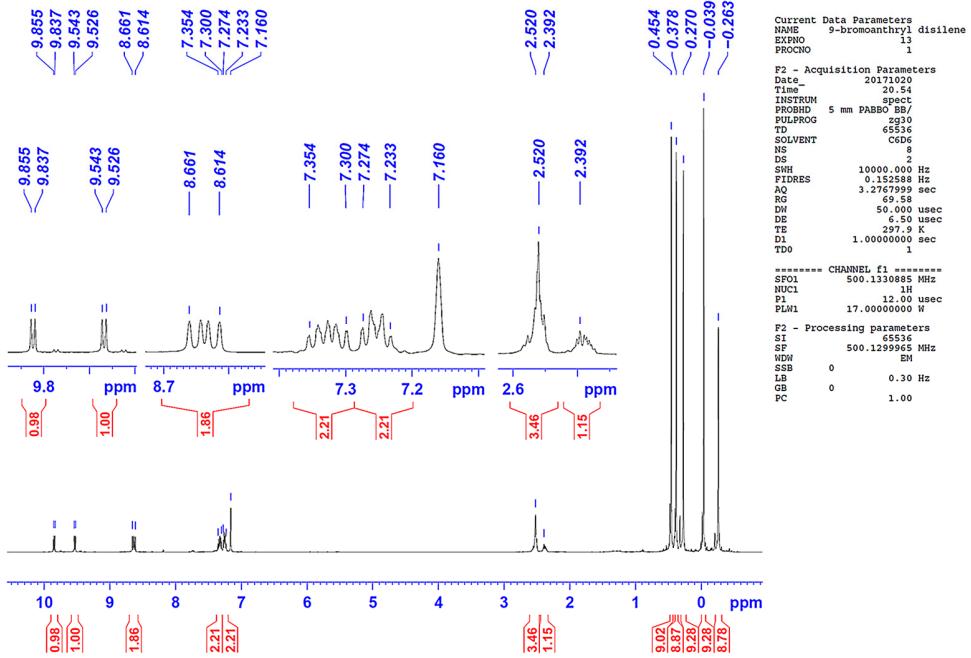


Figure S33. ^1H NMR spectrum of **6^{Br}** in C₆D₆ at rt.

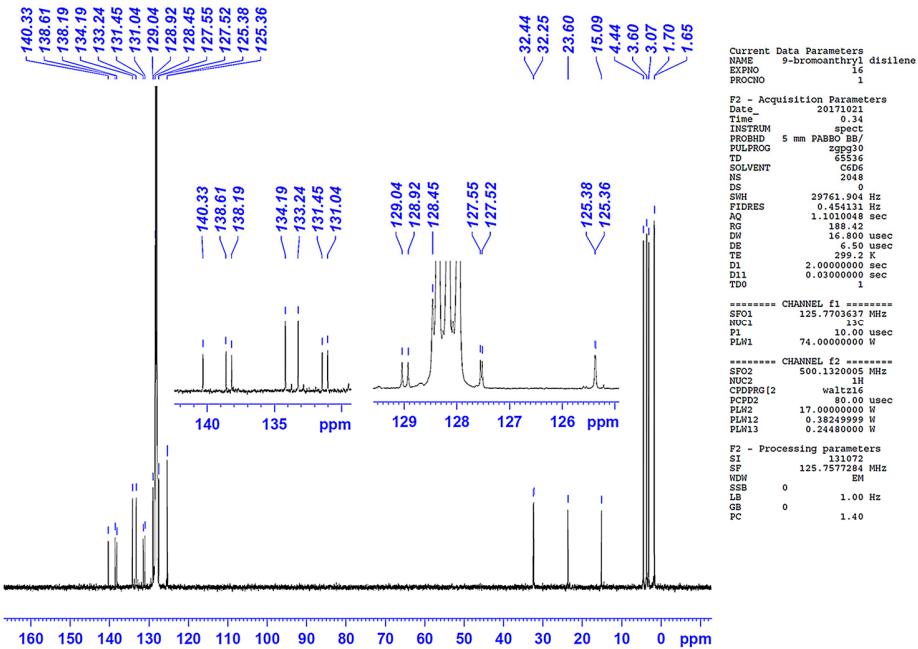


Figure S34. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **6^{Br}** in C₆D₆ at rt.

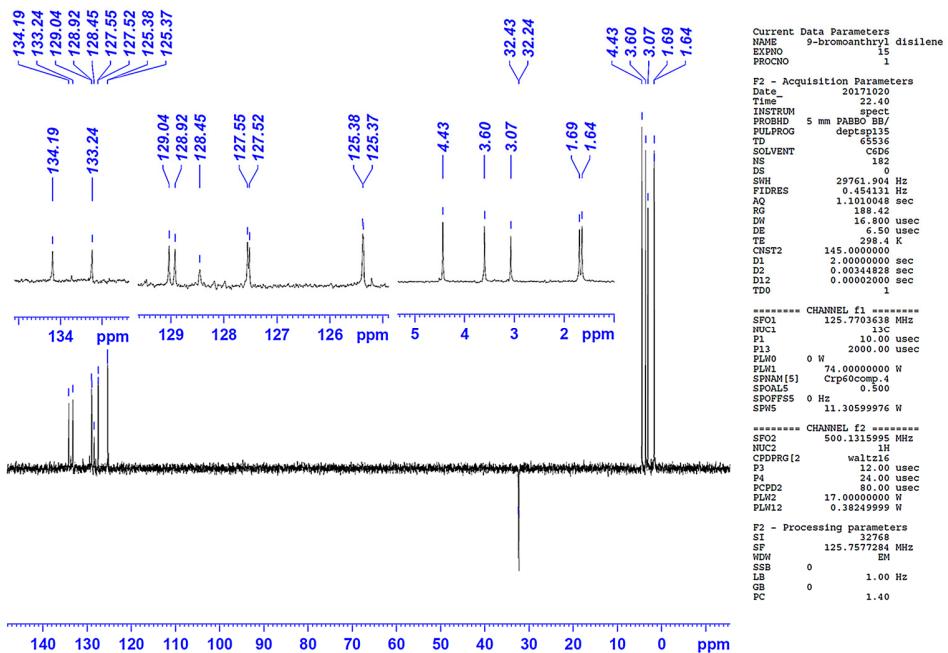


Figure S35. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **6^{Br}** using DEPT 135 pulse sequence in C₆D₆ at rt.

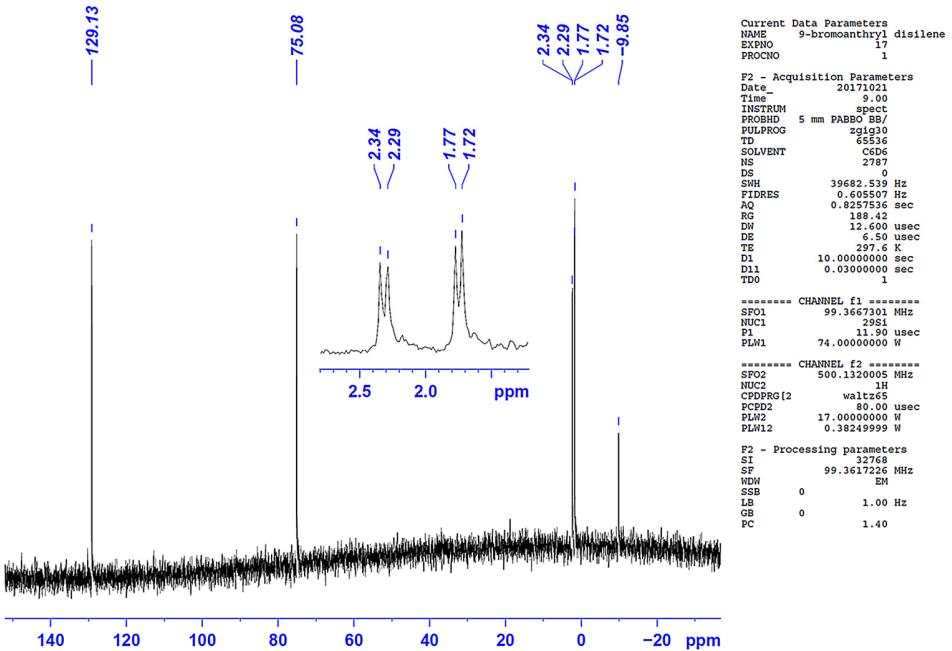


Figure S36. ^{29}Si { ^1H } NMR spectrum of **6^{Br}** using the inverse-gated pulse sequence in C₆D₆ at rt.

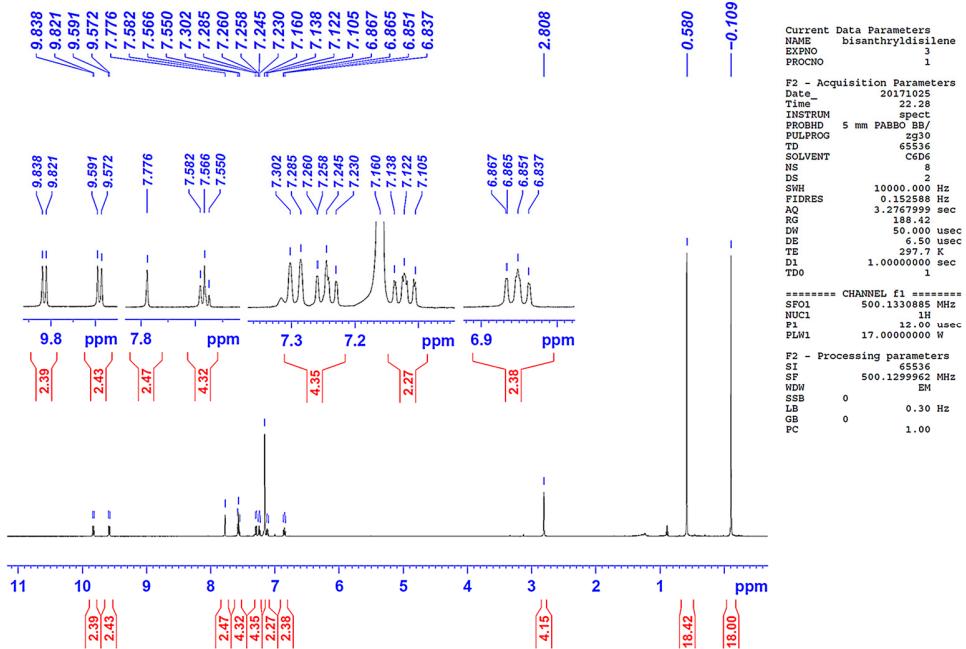


Figure S37. ^1H NMR spectrum of **7** in C_6D_6 at rt.

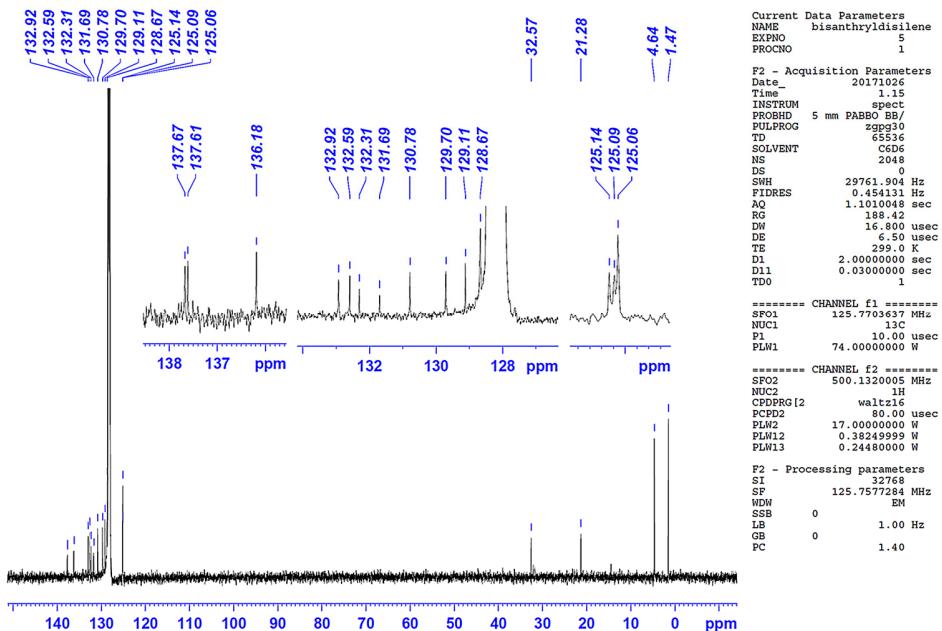


Figure S38. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **7** in C_6D_6 at rt.

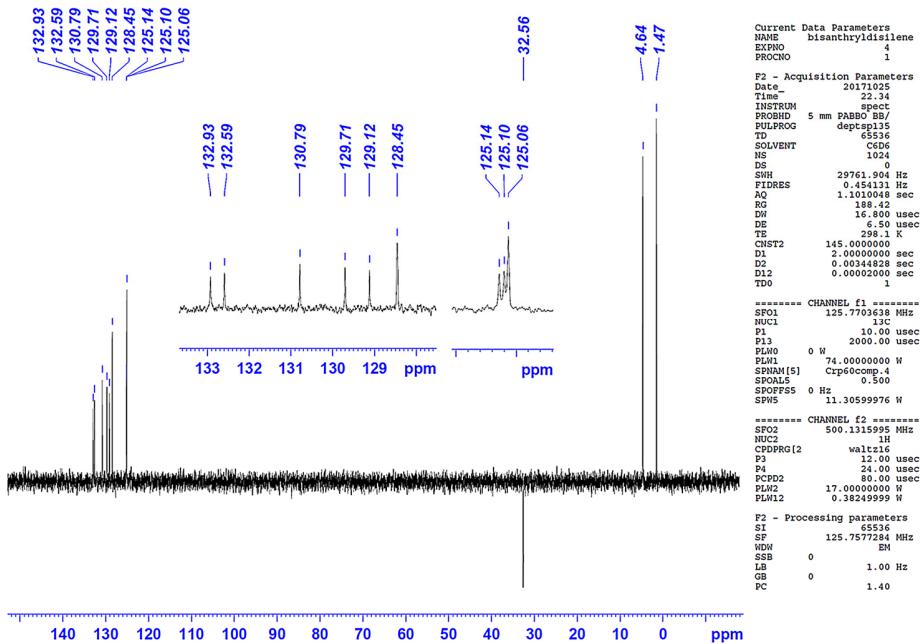


Figure S39. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of 7 using DEPT 135 pulse sequence in C_6D_6 at rt.

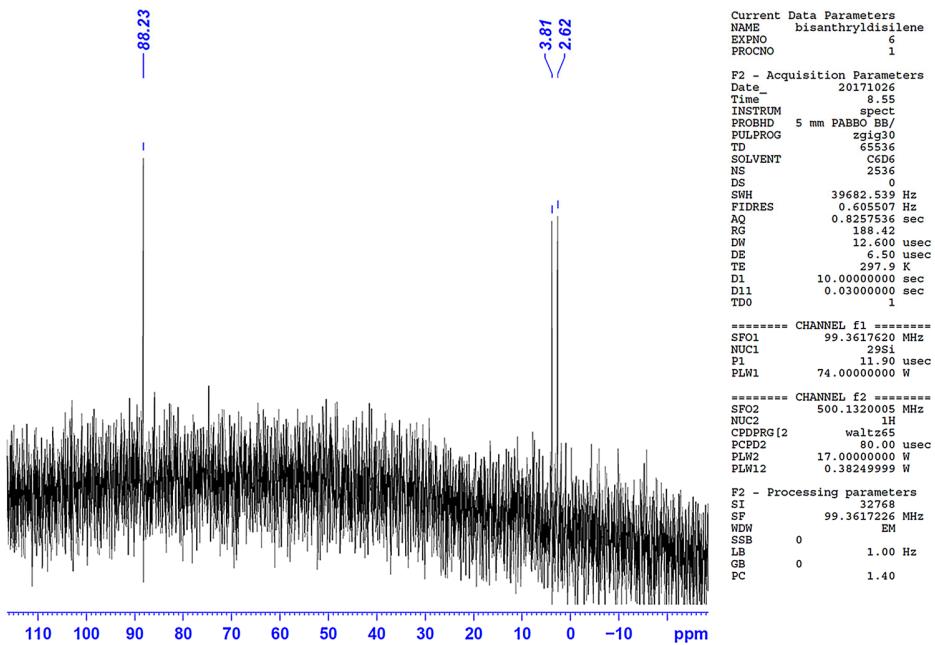


Figure S40. $^{29}\text{Si}\{\text{H}\}$ NMR spectrum of 7 using the inverse-gated pulse sequence in C_6D_6 at rt.

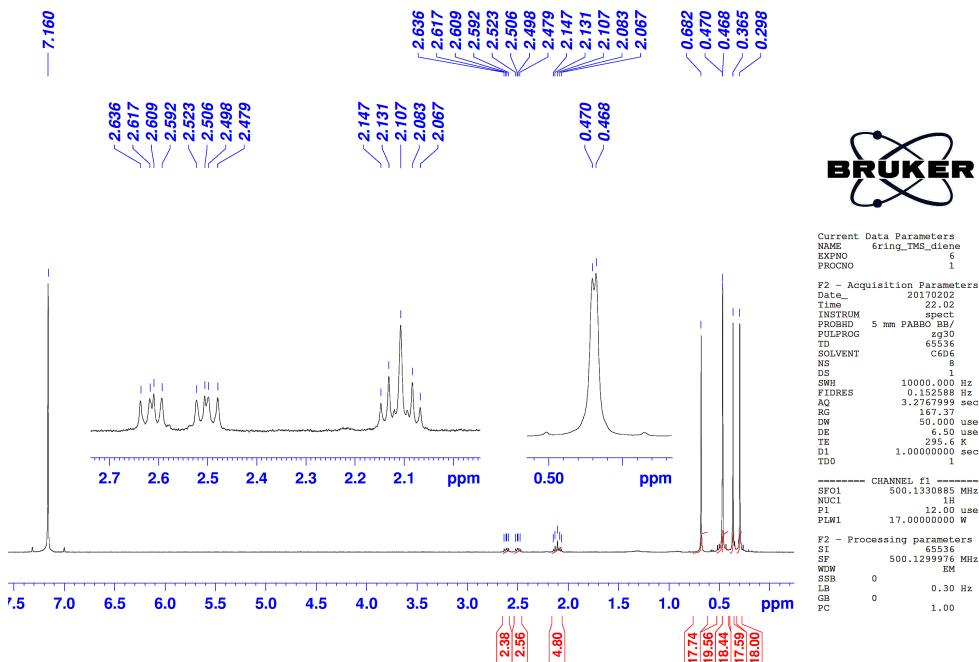


Figure S41. ^1H NMR spectrum of **8** in C_6D_6 at rt.

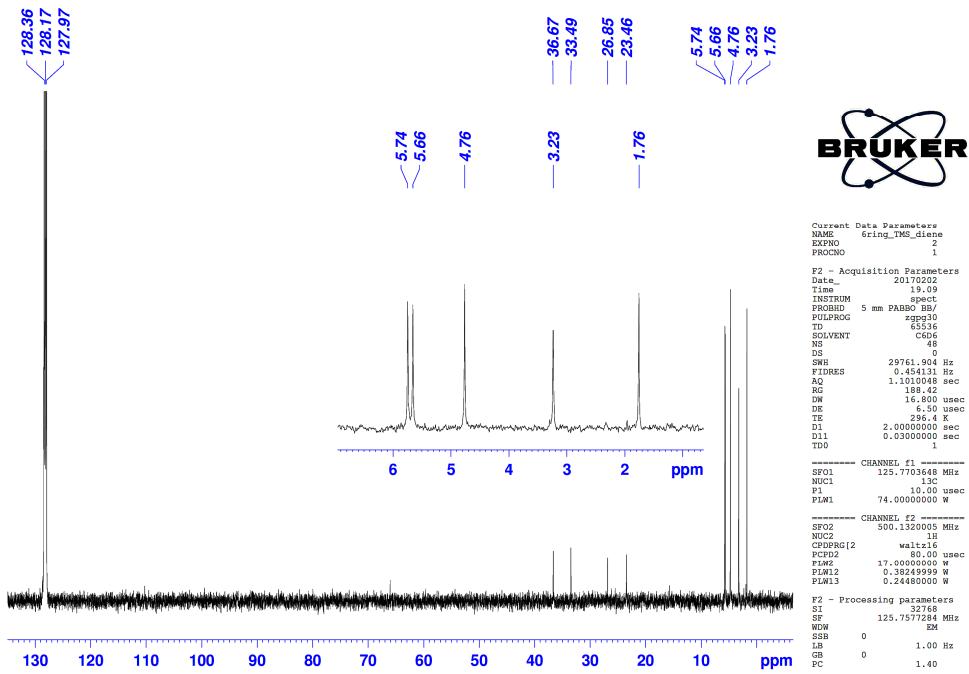


Figure S42. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **8** in C_6D_6 at rt.

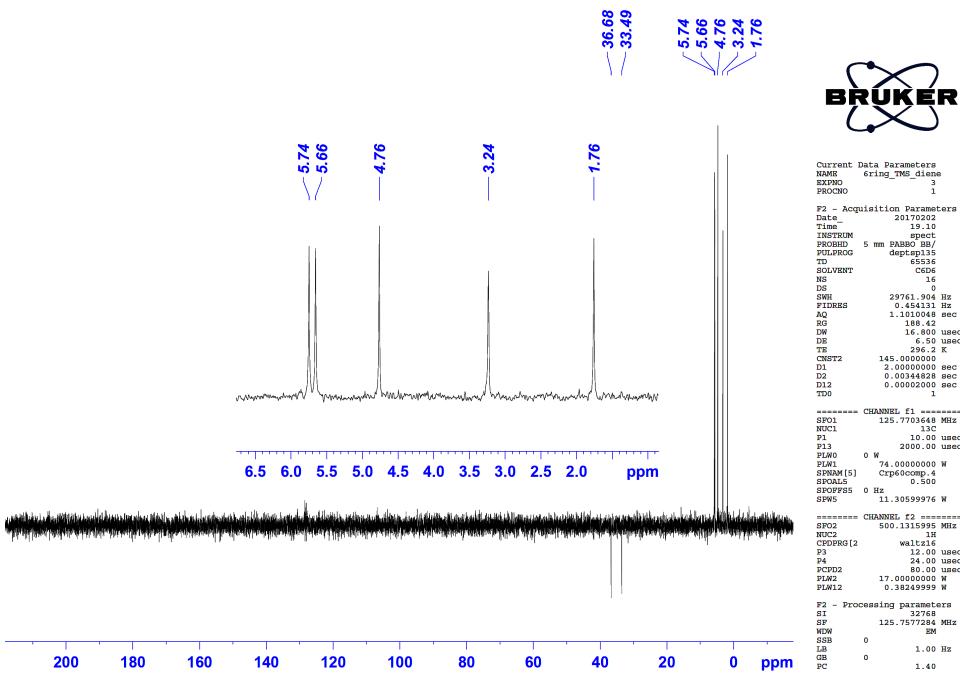


Figure S43. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of 8 using DEPT 135 pulse sequence in C_6D_6 at rt.

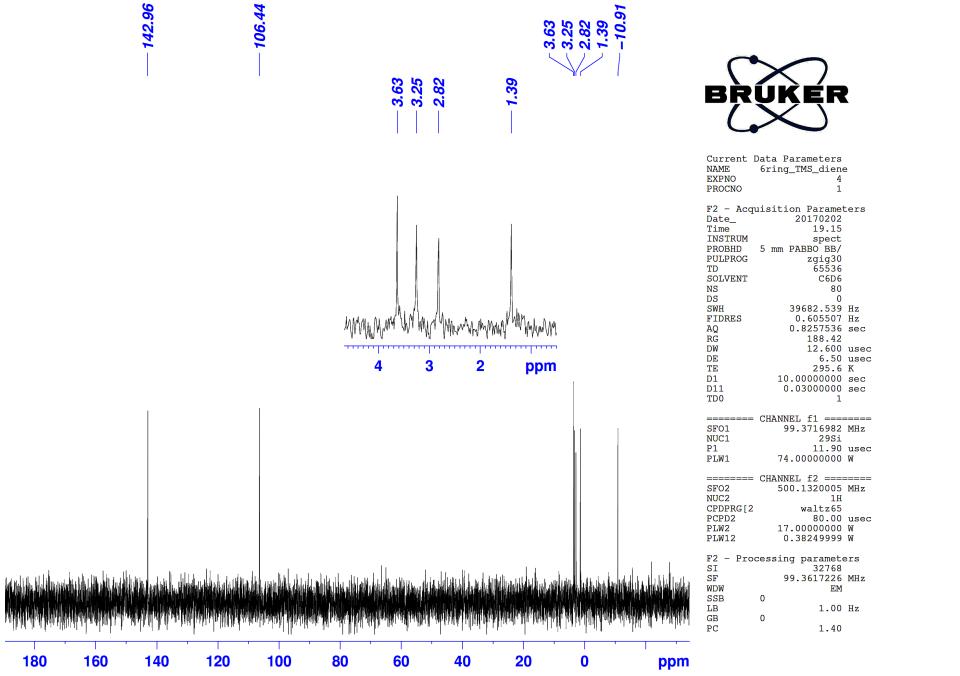


Figure S44. $^{29}\text{Si}\{\text{H}\}$ NMR spectrum of 8 using the inverse-gated pulse sequence in C_6D_6 at rt.

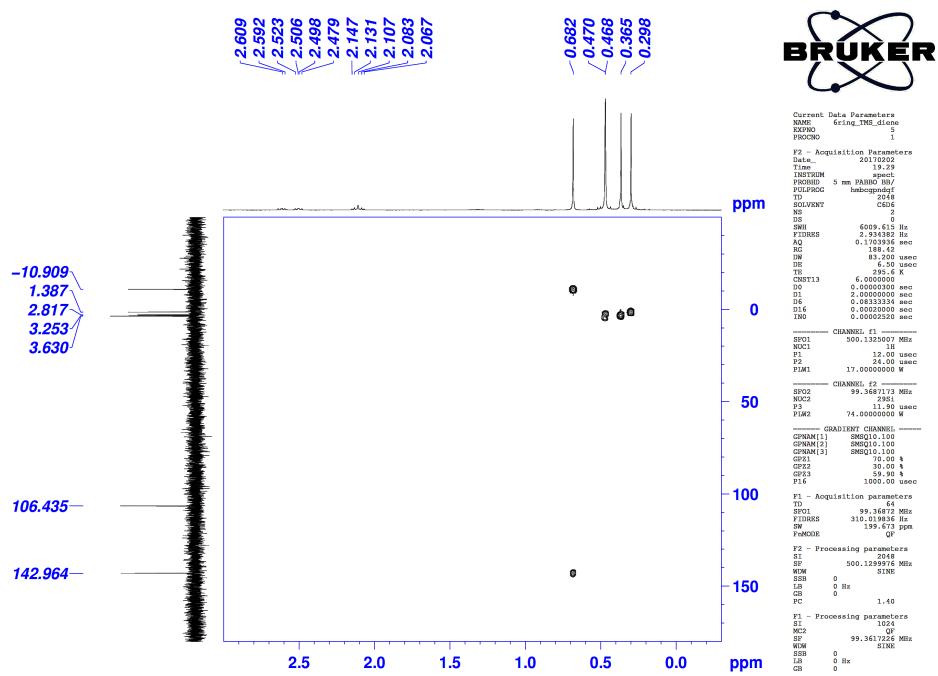


Figure S45. ^1H - ^{29}Si HMBC 2D NMR spectrum of **8** in C_6D_6 at rt.

2. UV-vis Spectra

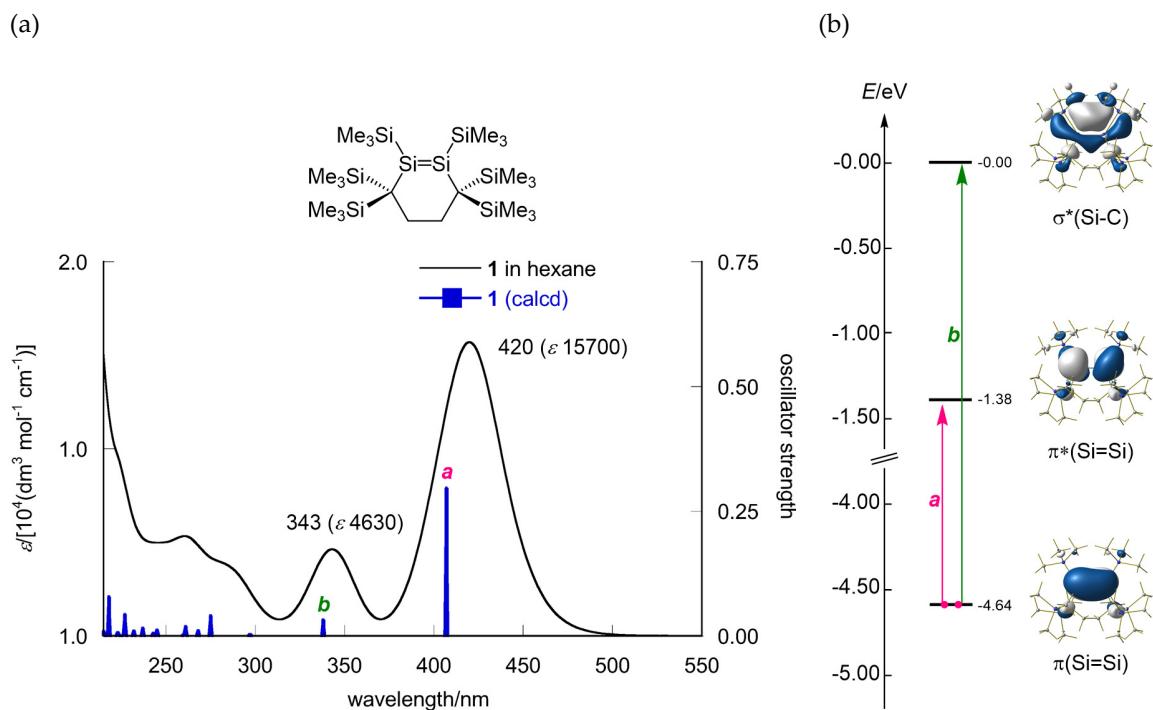


Figure S46. (a) UV-vis absorption spectra of **1** at room temperature in hexane (black line) as well as band positions and oscillator strengths (vertical blue bars) calculated at the TD-B3LYP-D3/6-311G(d)[hexane]/B3PW91-D3/6-31G(d) level of theory. (b) Selected frontier Kohn-Sham orbitals (isosurface value = 0.03) and major transitions.

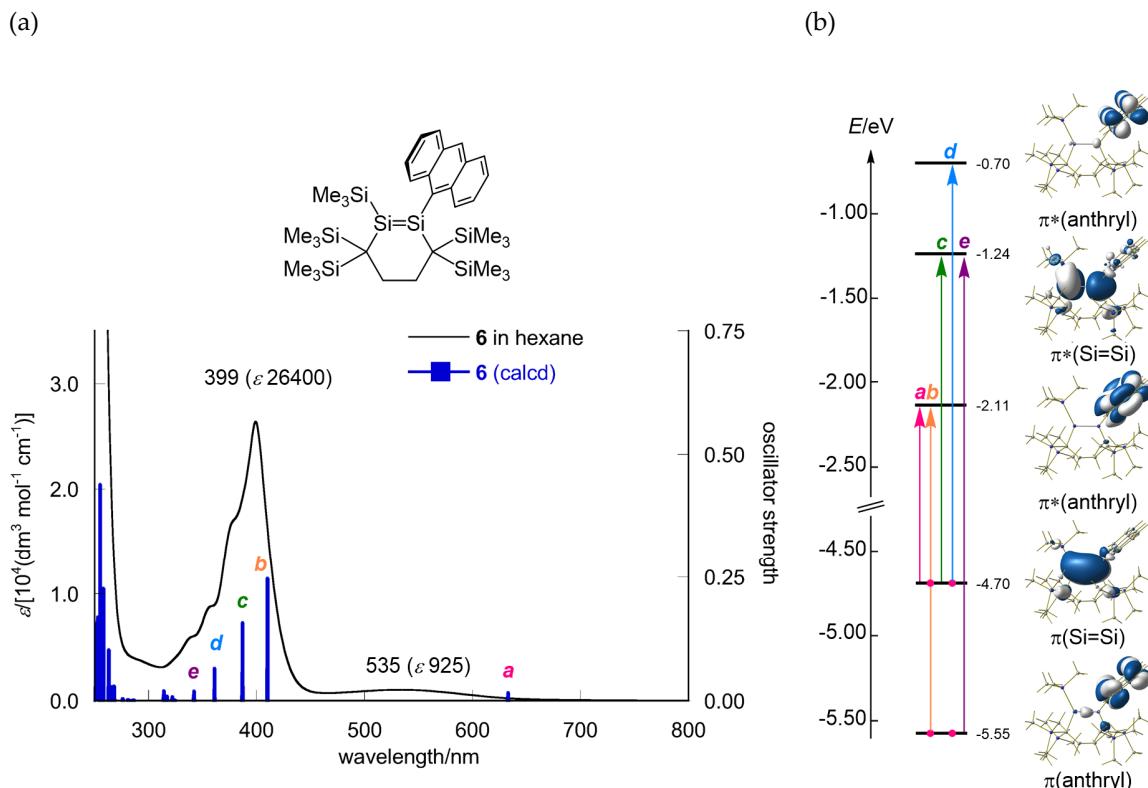


Figure S47. (a) UV-vis absorption spectra of **6** at room temperature in hexane (black line) and calculated band positions and oscillator strengths (vertical blue bars) calculated at the TD-B3LYP-D3/6-31G(d) [hexane]//B3PW91-D3/6-31G(d) level of theory. (b) Selected frontier Kohn-Sham orbitals (isosurface value = 0.03) and major transitions.

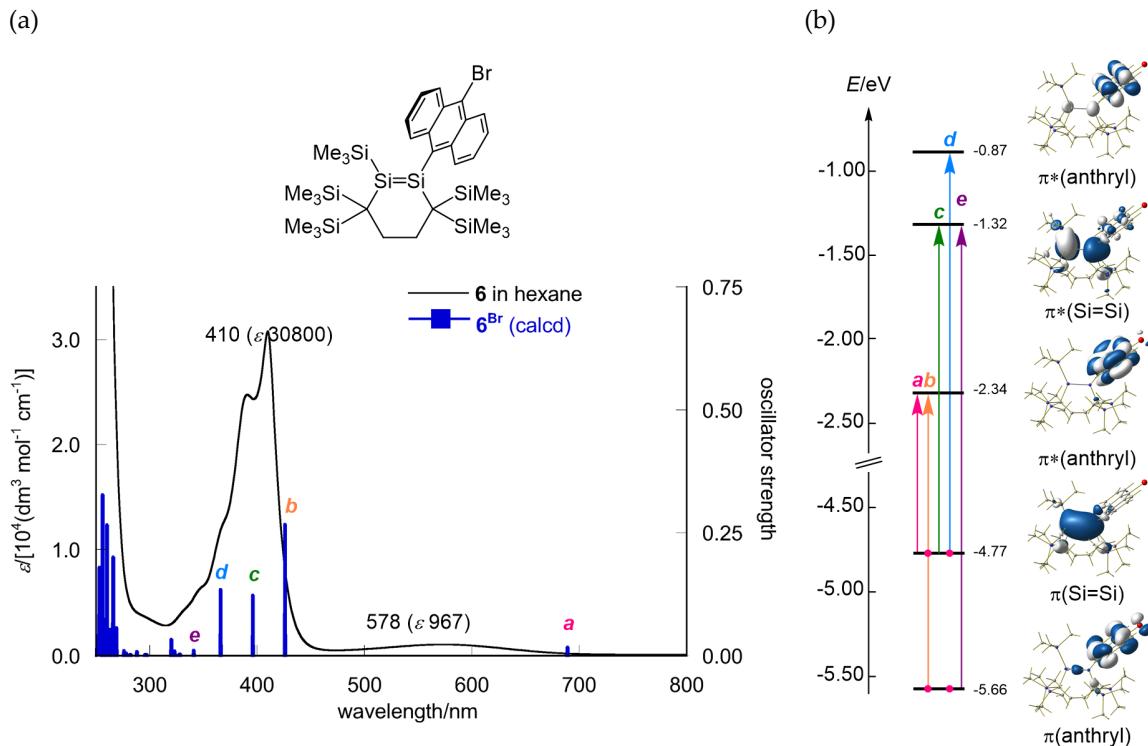


Figure S48. (a) UV-vis absorption spectra of **6^{Br}** at room temperature in hexane (black line) and calculated band positions and oscillator strengths (vertical blue bars) calculated at the TD-B3LYP-D3/6-31G(d) [hexane]/B3PW91-D3/6-31G(d) level of theory. (b) Selected frontier Kohn-Sham orbitals (isosurface value = 0.03) and major transitions.

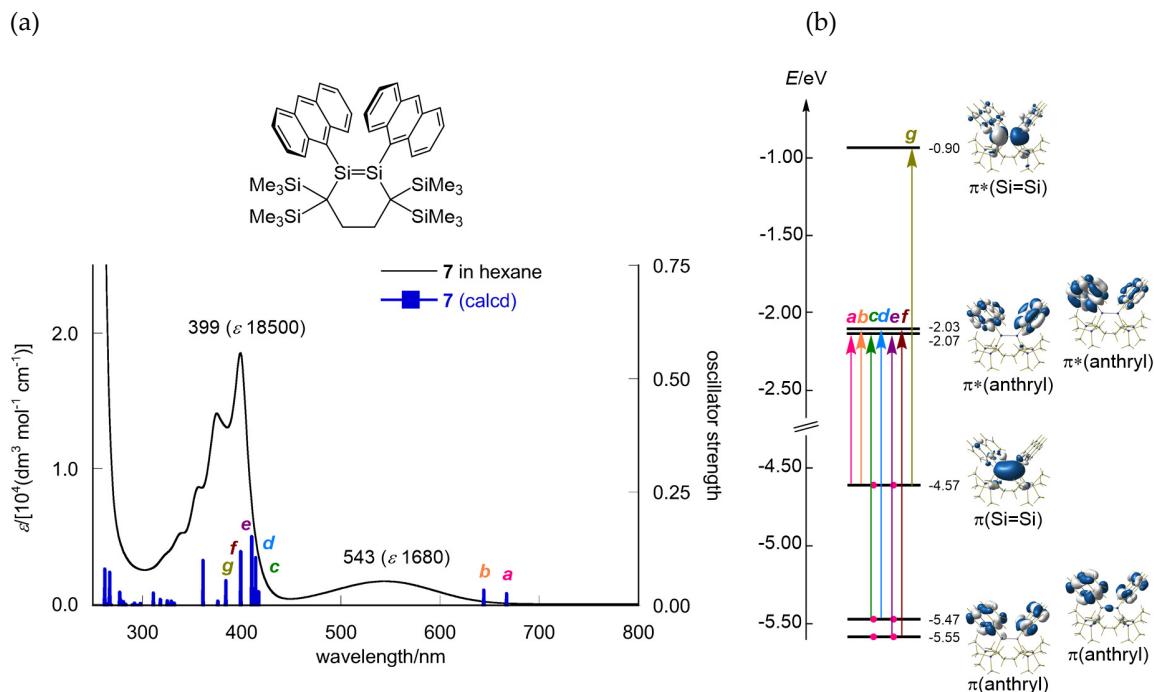


Figure S49. (a) UV-vis absorption spectra of **7** at room temperature in hexane (black line) and calculated band positions and oscillator strengths (vertical blue bars) calculated at the TD-B3LYP-D3/6-31G(d) [hexane]//B3PW91-D3/6-31G(d) level of theory. (b) Selected frontier Kohn-Sham orbitals (isosurface value = 0.03) and major transitions.

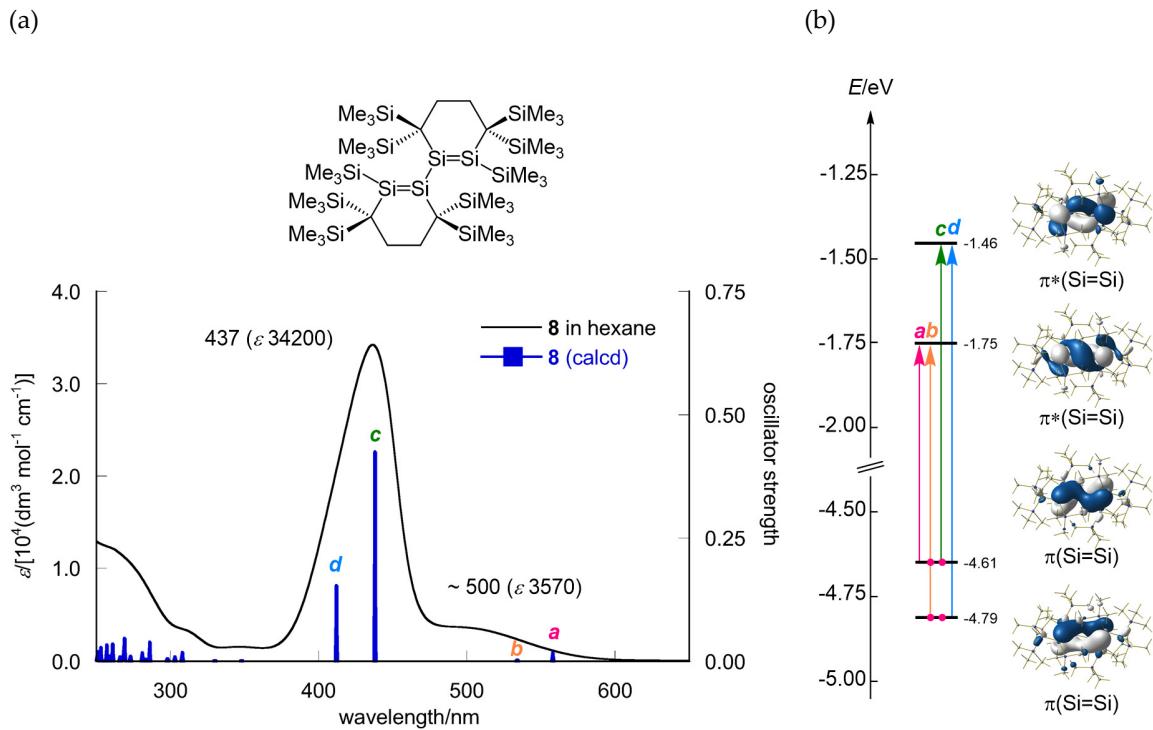


Figure S50. (a) UV-vis absorption spectra of **8** at room temperature in hexane (black line) and calculated band positions and oscillator strengths (vertical blue bars) calculated at the TD-B3LYP-D3/6-31G(d) [hexane]/B3PW91-D3/6-31G(d) level of theory. (b) Selected frontier Kohn-Sham orbitals (isosurface value = 0.03) and major transitions.

3. DFT Calculations

All theoretical calculations were performed using the Gaussian 09^{S1} and GRRM14^{S2} programs. Geometry optimizations and frequency analyses of **1**, **6**, **6^{Br}**, **7**, and **8** were carried out at the B3PW91-D3/6-31G(d) level of theory for all compounds. Imaginary frequencies were not found in any of the optimized structures. Atomic coordinates for these compounds are summarized in a .xyz file (optimized_structure_na04.xyz). The transition energies and oscillator strengths of the electron transitions of **1**, **6**, **6^{Br}**, **7**, and **8** were calculated using a time-dependent hybrid DFT method (TD DFT) at the B3LYP/6-311G(d) level of theory (Tables S1-S5). Selected Kohn-Sham orbitals of **1**, **6**, **6^{Br}**, **7**, and **8** are shown in Figures S46-S50, respectively. Selected structural parameters and spectral data were summarized in Table S6.

Calculated Transition Energies and Oscillator Strengths of the Electron Transitions

Table S1. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of 1

Excited State	1:	Singlet-A	3.0400 eV	407.84 nm	f=0.2970	<S**2>=0.000
151 ->152		0.69541				
151 ->153		0.11294				
Excited State	2:	Singlet-A	3.6708 eV	337.76 nm	f=0.0325	<S**2>=0.000
151 ->152		-0.11132				
151 ->153		0.69259				
Excited State	3:	Singlet-A	4.1756 eV	296.93 nm	f=0.0033	<S**2>=0.000
150 ->152		0.69227				
151 ->155		0.10556				
Excited State	4:	Singlet-A	4.3616 eV	284.27 nm	f=0.0003	<S**2>=0.000
151 ->155		0.68344				
151 ->159		0.11496				
Excited State	5:	Singlet-A	4.5099 eV	274.92 nm	f=0.0410	<S**2>=0.000
149 ->152		-0.18045				
151 ->154		0.67327				
Excited State	6:	Singlet-A	4.6192 eV	268.41 nm	f=0.0108	<S**2>=0.000
149 ->152		0.63398				
151 ->154		0.20058				
151 ->156		-0.21182				
Excited State	7:	Singlet-A	4.7439 eV	261.35 nm	f=0.0194	<S**2>=0.000
149 ->152		0.24149				
151 ->156		0.64524				
Excited State	8:	Singlet-A	4.7761 eV	259.60 nm	f=0.0030	<S**2>=0.000
151 ->157		0.64430				
151 ->159		-0.24075				
Excited State	9:	Singlet-A	5.0575 eV	245.15 nm	f=0.0121	<S**2>=0.000
147 ->152		-0.20212				
148 ->152		0.56935				
151 ->158		-0.34352				
Excited State	10:	Singlet-A	5.1125 eV	242.51 nm	f=0.0058	<S**2>=0.000
147 ->152		-0.17502				
148 ->152		0.30887				
151 ->158		0.58868				
151 ->159		-0.13291				
Excited State	11:	Singlet-A	5.1435 eV	241.05 nm	f=0.0000	<S**2>=0.000
151 ->157		0.25934				
151 ->158		0.14198				
151 ->159		0.62935				
Excited State	12:	Singlet-A	5.2392 eV	236.65 nm	f=0.0053	<S**2>=0.000
151 ->156		0.12813				
151 ->160		0.68417				
Excited State	13:	Singlet-A	5.2421 eV	236.51 nm	f=0.0160	<S**2>=0.000
147 ->152		0.64637				

148 ->152		0.26122				
Excited State 14:	Singlet-A	5.3532 eV	231.61 nm	f=0.0103	<S**2>=0.000	
151 ->161		0.67455				
Excited State 15:	Singlet-A	5.4548 eV	227.29 nm	f=0.0434	<S**2>=0.000	
150 ->153		-0.21307				
151 ->162		0.58727				
151 ->163		-0.30095				
Excited State 16:	Singlet-A	5.4765 eV	226.39 nm	f=0.0008	<S**2>=0.000	
146 ->152		0.70082				
Excited State 17:	Singlet-A	5.5720 eV	222.51 nm	f=0.0071	<S**2>=0.000	
151 ->162		0.31612				
151 ->163		0.61477				
Excited State 18:	Singlet-A	5.6991 eV	217.55 nm	f=0.0789	<S**2>=0.000	
150 ->153		0.63864				
151 ->162		0.19558				
151 ->163		-0.10860				
151 ->165		0.10638				
Excited State 19:	Singlet-A	5.7695 eV	214.90 nm	f=0.0099	<S**2>=0.000	
151 ->161		-0.10744				
151 ->164		0.66255				
151 ->167		0.18075				
Excited State 20:	Singlet-A	5.8205 eV	213.01 nm	f=0.0125	<S**2>=0.000	
150 ->153		-0.11215				
151 ->165		0.67262				
151 ->169		-0.11097				
Excited State 21:	Singlet-A	5.8938 eV	210.36 nm	f=0.0009	<S**2>=0.000	
143 ->152		-0.12073				
145 ->152		0.68561				
Excited State 22:	Singlet-A	5.9183 eV	209.49 nm	f=0.0010	<S**2>=0.000	
142 ->152		-0.13001				
144 ->152		0.65459				
151 ->167		-0.15955				
151 ->168		-0.14458				
Excited State 23:	Singlet-A	5.9274 eV	209.17 nm	f=0.0097	<S**2>=0.000	
144 ->152		0.12320				
151 ->164		-0.20175				
151 ->167		0.61530				
151 ->168		-0.13112				
151 ->171		0.11668				
Excited State 24:	Singlet-A	5.9320 eV	209.01 nm	f=0.0004	<S**2>=0.000	
151 ->166		0.65925				
151 ->169		0.16228				
Excited State 25:	Singlet-A	5.9655 eV	207.84 nm	f=0.0045	<S**2>=0.000	
144 ->152		0.18394				
151 ->167		0.14167				
151 ->168		0.62601				
151 ->171		-0.16672				
Excited State 26:	Singlet-A	6.0047 eV	206.48 nm	f=0.0018	<S**2>=0.000	
141 ->152		0.10446				
143 ->152		0.67519				
145 ->152		0.11491				
151 ->169		-0.11576				
Excited State 27:	Singlet-A	6.0214 eV	205.91 nm	f=0.0061	<S**2>=0.000	

143 ->152	0.11546	
151 ->165	0.12130	
151 ->166	-0.15733	
151 ->169	0.64851	
Excited State 28:	Singlet-A	6.0637 eV 204.47 nm f=0.0147 <S**2>=0.000
136 ->152	0.16657	
139 ->152	-0.13126	
140 ->152	-0.38745	
142 ->152	0.40989	
149 ->153	0.34779	
Excited State 29:	Singlet-A	6.0873 eV 203.68 nm f=0.0631 <S**2>=0.000
139 ->152	0.14445	
140 ->152	0.20109	
142 ->152	-0.22046	
149 ->153	0.57382	
151 ->171	0.16947	
Excited State 30:	Singlet-A	6.0894 eV 203.61 nm f=0.0111 <S**2>=0.000
142 ->152	0.13117	
149 ->153	-0.13712	
151 ->168	0.19133	
151 ->171	0.61928	
Excited State 31:	Singlet-A	6.1198 eV 202.60 nm f=0.0016 <S**2>=0.000
136 ->152	-0.15829	
140 ->152	0.45031	
142 ->152	0.48896	
144 ->152	0.11550	
Excited State 32:	Singlet-A	6.1257 eV 202.40 nm f=0.0576 <S**2>=0.000
138 ->152	0.26970	
141 ->152	0.60533	
151 ->170	-0.19014	

JOB name: ti552Si2TD
Method/Basis: TD-B3LYP-D3/6-311G(d) [hexane]

Table S2. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of **6**

Excited State 1:	Singlet-A	1.9565 eV 633.71 nm f=0.0166 <S**2>=0.000
177 ->178	0.70501	
Excited State 2:	Singlet-A	3.0231 eV 410.13 nm f=0.2474 <S**2>=0.000
176 ->178	0.66314	
177 ->179	-0.22931	
Excited State 3:	Singlet-A	3.2023 eV 387.17 nm f=0.1577 <S**2>=0.000
176 ->178	0.21627	
177 ->179	0.61532	
177 ->180	0.24484	
Excited State 4:	Singlet-A	3.4339 eV 361.06 nm f=0.0655 <S**2>=0.000
177 ->179	-0.22178	
177 ->180	0.65704	
Excited State 5:	Singlet-A	3.6297 eV 341.58 nm f=0.0202 <S**2>=0.000
174 ->178	0.18245	
176 ->179	0.66889	

Excited State	6:	Singlet-A	3.8250 eV	324.14 nm	f=0.0017 <S**2>=0.000
	177 ->182	0.68259			
	177 ->183	0.10647			
	177 ->184	0.11108			
Excited State	7:	Singlet-A	3.8451 eV	322.45 nm	f=0.0085 <S**2>=0.000
	174 ->178	0.47359			
	175 ->178	-0.12519			
	176 ->179	-0.17249			
	176 ->180	0.46745			
Excited State	8:	Singlet-A	3.9064 eV	317.39 nm	f=0.0094 <S**2>=0.000
	175 ->178	0.27917			
	177 ->181	0.63857			
Excited State	9:	Singlet-A	3.9495 eV	313.92 nm	f=0.0203 <S**2>=0.000
	175 ->178	0.62923			
	177 ->181	-0.28391			
Excited State	10:	Singlet-A	4.3424 eV	285.52 nm	f=0.0021 <S**2>=0.000
	173 ->178	0.69215			
Excited State	11:	Singlet-A	4.3895 eV	282.45 nm	f=0.0009 <S**2>=0.000
	172 ->178	0.23107			
	177 ->182	-0.14114			
	177 ->183	0.55755			
	177 ->184	0.30019			
Excited State	12:	Singlet-A	4.4155 eV	280.79 nm	f=0.0024 <S**2>=0.000
	171 ->178	-0.15425			
	172 ->178	0.58017			
	176 ->181	0.24536			
	177 ->183	-0.22592			
	177 ->184	-0.10468			
Excited State	13:	Singlet-A	4.4853 eV	276.42 nm	f=0.0047 <S**2>=0.000
	175 ->179	0.67047			
Excited State	14:	Singlet-A	4.6350 eV	267.50 nm	f=0.0299 <S**2>=0.000
	170 ->178	-0.13086			
	171 ->178	0.57194			
	172 ->178	0.20292			
	174 ->178	0.12394			
	176 ->180	-0.12260			
	176 ->181	-0.16400			
	177 ->184	0.15656			
Excited State	15:	Singlet-A	4.6617 eV	265.96 nm	f=0.0288 <S**2>=0.000
	171 ->178	-0.27025			
	174 ->178	0.11485			
	176 ->180	-0.13206			
	176 ->181	-0.12995			
	177 ->183	-0.29062			
	177 ->184	0.51164			
Excited State	16:	Singlet-A	4.7166 eV	262.87 nm	f=0.1032 <S**2>=0.000
	171 ->178	-0.17003			
	174 ->178	0.16091			
	176 ->180	-0.18119			
	176 ->181	-0.26459			
	177 ->184	-0.22489			
	177 ->185	0.50165			
Excited State	17:	Singlet-A	4.8010 eV	258.25 nm	f=0.2271 <S**2>=0.000
	172 ->178	-0.18268			
	174 ->178	0.20127			
	176 ->180	-0.21204			

176 ->181	0.50189
176 ->182	-0.24105
177 ->185	0.17826
 Excited State 18:	Singlet-A
172 ->178	-0.10986
176 ->181	0.21104
176 ->182	0.59909
177 ->185	0.11718
177 ->186	0.13187
 Excited State 19:	Singlet-A
173 ->179	-0.28558
174 ->178	-0.23010
174 ->179	-0.11967
176 ->180	0.25067
176 ->182	-0.17684
177 ->184	0.13152
177 ->185	0.30505
177 ->186	0.31989
 Excited State 20:	Singlet-A
169 ->178	-0.28092
170 ->178	0.43492
171 ->178	0.10637
173 ->179	0.19644
174 ->178	-0.14883
176 ->180	0.15845
176 ->182	0.11061
177 ->185	0.16126
177 ->186	-0.22930
 Excited State 21:	Singlet-A
169 ->178	-0.18758
170 ->178	0.29463
174 ->178	0.14431
174 ->179	0.17878
176 ->180	-0.15481
177 ->185	-0.13998
177 ->186	0.47307
177 ->188	0.11539
 Excited State 22:	Singlet-A
169 ->178	0.10053
170 ->178	-0.21964
173 ->179	0.58801
174 ->178	-0.10106
176 ->180	0.11071
177 ->185	0.10790
177 ->186	0.18098
 Excited State 23:	Singlet-A
174 ->178	-0.10697
174 ->179	0.65726
176 ->180	0.13630
 Excited State 24:	Singlet-A
167 ->178	-0.13156
169 ->178	0.55224
170 ->178	0.36976
171 ->178	0.11133
 Excited State 25:	Singlet-A
168 ->178	-0.20468
177 ->187	0.65144
 Excited State 26:	Singlet-A
	5.2074 eV 238.09 nm f=0.0059 <S**2>=0.000

165 ->178	-0.10564	
166 ->178	-0.12427	
168 ->178	0.63185	
177 ->187	0.20514	
Excited State 27:	Singlet-A	5.2377 eV 236.71 nm f=0.0229 <S**2>=0.000
177 ->186	-0.15360	
177 ->188	0.64506	
177 ->189	0.18551	
Excited State 28:	Singlet-A	5.2828 eV 234.69 nm f=0.0218 <S**2>=0.000
171 ->179	0.47403	
172 ->179	0.49218	
Excited State 29:	Singlet-A	5.3326 eV 232.50 nm f=0.0030 <S**2>=0.000
162 ->178	-0.10286	
163 ->178	-0.10796	
165 ->178	0.18812	
166 ->178	0.44992	
167 ->178	-0.37685	
168 ->178	0.15857	
171 ->179	0.13863	
172 ->179	-0.11789	
Excited State 30:	Singlet-A	5.3520 eV 231.66 nm f=0.0033 <S**2>=0.000
167 ->178	0.18670	
171 ->179	0.46074	
172 ->179	-0.41742	
174 ->181	0.12188	
Excited State 31:	Singlet-A	5.3727 eV 230.77 nm f=0.1079 <S**2>=0.000
175 ->180	0.67105	
Excited State 32:	Singlet-A	5.3933 eV 229.88 nm f=0.0025 <S**2>=0.000
158 ->178	0.11214	
160 ->178	0.10381	
163 ->178	0.22042	
166 ->178	0.43094	
167 ->178	0.35261	
169 ->178	0.16244	
176 ->183	-0.16746	

JOB name: ti552SiAntTD
Method/Basis: TD-B3LYP-D3/6-311G(d) [hexane]

Table S3. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of **6^{Br}**

Excited State 1:	Singlet-A	1.7996 eV 688.97 nm f=0.0177 <S**2>=0.000
194 ->195	0.70538	
Excited State 2:	Singlet-A	2.9114 eV 425.86 nm f=0.2676 <S**2>=0.000
193 ->195	0.68615	
194 ->196	0.15154	
Excited State 3:	Singlet-A	3.1308 eV 396.02 nm f=0.1236 <S**2>=0.000
193 ->195	-0.12562	
194 ->196	0.59830	
194 ->197	0.34249	

Excited State 4: Singlet-A 3.3836 eV 366.42 nm f=0.1352 <S**2>=0.000
 194 ->196 -0.31852
 194 ->197 0.61195

Excited State 5: Singlet-A 3.6388 eV 340.73 nm f=0.0115 <S**2>=0.000
 191 ->195 0.27888
 193 ->196 0.62476
 193 ->197 0.13825

Excited State 6: Singlet-A 3.7775 eV 328.21 nm f=0.0039 <S**2>=0.000
 191 ->195 0.10305
 192 ->195 0.66044
 193 ->197 0.12545
 194 ->198 0.14762

Excited State 7: Singlet-A 3.8154 eV 324.96 nm f=0.0012 <S**2>=0.000
 194 ->198 0.13665
 194 ->199 -0.41200
 194 ->200 0.52334
 194 ->201 -0.11232

Excited State 8: Singlet-A 3.8355 eV 323.26 nm f=0.0106 <S**2>=0.000
 191 ->195 0.40365
 192 ->195 -0.15267
 193 ->196 -0.27829
 193 ->197 0.45480
 194 ->198 -0.12099

Excited State 9: Singlet-A 3.8720 eV 320.21 nm f=0.0339 <S**2>=0.000
 192 ->195 -0.14925
 194 ->198 0.65772
 194 ->199 0.10227

Excited State 10: Singlet-A 4.1814 eV 296.51 nm f=0.0021 <S**2>=0.000
 190 ->195 0.68459
 191 ->195 -0.12979

Excited State 11: Singlet-A 4.1938 eV 295.64 nm f=0.0035 <S**2>=0.000
 194 ->199 0.55278
 194 ->200 0.41903

Excited State 12: Singlet-A 4.3096 eV 287.69 nm f=0.0009 <S**2>=0.000
 188 ->195 0.47037
 189 ->195 0.46733
 193 ->198 0.18694

Excited State 13: Singlet-A 4.3897 eV 282.44 nm f=0.0032 <S**2>=0.000
 194 ->200 0.16879
 194 ->201 0.61074
 194 ->202 0.27660

Excited State 14: Singlet-A 4.4656 eV 277.64 nm f=0.0059 <S**2>=0.000
 187 ->195 0.15563
 188 ->195 -0.46440
 189 ->195 0.48681

Excited State 15: Singlet-A 4.4850 eV 276.44 nm f=0.0109 <S**2>=0.000
 192 ->196 0.66513
 193 ->197 -0.10895

Excited State 16: Singlet-A 4.6141 eV 268.71 nm f=0.0574 <S**2>=0.000
 186 ->195 -0.29108
 191 ->195 0.14619
 193 ->197 -0.15321
 193 ->198 -0.30360
 193 ->199 0.42310
 194 ->201 0.10261
 194 ->202 -0.14912
 194 ->203 -0.13315

Excited State 17: Singlet-A 4.6565 eV 266.26 nm f=0.2016 <S**2>=0.000
 186 ->195 0.41888
 187 ->195 -0.10662
 191 ->195 0.24267
 193 ->197 -0.25105
 193 ->199 -0.16420
 193 ->200 0.10821
 194 ->201 0.12089
 194 ->202 -0.24690
 194 ->203 -0.18467

Excited State 18: Singlet-A 4.6840 eV 264.70 nm f=0.0374 <S**2>=0.000
 186 ->195 0.33232
 187 ->195 -0.15425
 193 ->199 0.41629
 193 ->200 0.33371
 194 ->202 0.12708

Excited State 19: Singlet-A 4.7138 eV 263.02 nm f=0.0538 <S**2>=0.000
 193 ->198 -0.11088
 194 ->201 -0.20724
 194 ->202 0.48250
 194 ->203 -0.40719

Excited State 20: Singlet-A 4.7589 eV 260.53 nm f=0.0555 <S**2>=0.000
 185 ->195 -0.26408
 186 ->195 0.12378
 187 ->195 0.55551
 189 ->195 -0.11206
 193 ->198 0.20379

Excited State 21: Singlet-A 4.7740 eV 259.70 nm f=0.2667 <S**2>=0.000
 185 ->195 0.10229
 186 ->195 -0.17695
 187 ->195 -0.18572
 188 ->195 -0.16427
 191 ->195 0.20136
 193 ->197 -0.22378
 193 ->198 0.50029
 193 ->199 0.12316

Excited State 22: Singlet-A 4.8363 eV 256.36 nm f=0.3279 <S**2>=0.000
 190 ->196 -0.19562
 191 ->195 0.18601
 193 ->197 -0.19628
 193 ->198 -0.17735
 194 ->202 0.22006
 194 ->203 0.43261
 194 ->204 0.22653

Excited State 23: Singlet-A 4.8784 eV 254.15 nm f=0.0025 <S**2>=0.000
 182 ->195 0.47576
 183 ->195 0.11262
 185 ->195 -0.37544
 187 ->195 -0.19130
 190 ->196 0.18364
 194 ->204 -0.13890

Excited State 24: Singlet-A 4.8890 eV 253.60 nm f=0.0127 <S**2>=0.000
 182 ->195 0.47029
 185 ->195 0.43001
 187 ->195 0.20983

Excited State 25: Singlet-A 4.9011 eV 252.97 nm f=0.1804 <S**2>=0.000
 182 ->195 -0.16967
 185 ->195 0.13415
 190 ->196 0.38611
 191 ->195 0.15447
 193 ->197 -0.15705
 194 ->203 0.22289
 194 ->204 -0.38490

Excited State 26: Singlet-A 4.9298 eV 251.50 nm f=0.0133 <S**2>=0.000
 190 ->196 0.47877
 191 ->196 -0.10557
 193 ->200 0.10400
 194 ->204 0.45026

Excited State 27: Singlet-A 4.9444 eV 250.76 nm f=0.0408 <S**2>=0.000
 186 ->195 -0.22665
 193 ->199 -0.27234
 193 ->200 0.55908
 194 ->204 -0.13428

Excited State 28: Singlet-A 5.0342 eV 246.28 nm f=0.0057 <S**2>=0.000
 179 ->195 0.17358
 181 ->195 -0.10104
 184 ->195 0.65680

Excited State 29: Singlet-A 5.0804 eV 244.04 nm f=0.0296 <S**2>=0.000
 190 ->196 0.14662
 191 ->196 0.66492

Excited State 30: Singlet-A 5.1645 eV 240.07 nm f=0.0010 <S**2>=0.000
 177 ->195 0.11600
 178 ->195 -0.14048
 179 ->195 -0.16235
 180 ->195 0.14241
 181 ->195 0.49584
 183 ->195 -0.36126
 184 ->195 0.16846

Excited State 31: Singlet-A 5.2196 eV 237.53 nm f=0.0032 <S**2>=0.000
 174 ->195 0.11680
 178 ->195 0.14165
 179 ->195 -0.19923
 180 ->195 0.17284
 181 ->195 0.28490
 183 ->195 0.46685
 185 ->195 0.17380

194 ->205	0.16393			
194 ->206	0.10927			
Excited State 32:	Singlet-A	5.2274 eV	237.18 nm	f=0.0239 <S**2>=0.000
179 ->195	0.12910			
180 ->195	-0.10591			
183 ->195	-0.13134			
189 ->196	0.15291			
194 ->205	0.58957			
194 ->206	0.23163			

JOB name: ti552SiAntBrTD
Method/Basis: TD-B3LYP-D3/6-311G(d) [hexane]

Table S4. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of **7**

Excited State 1:	Singlet-A	1.8590 eV	666.96 nm	f=0.0265 <S**2>=0.000
203 -> 204	0.69351			
203 -> 205	0.12643			
Excited State 2:	Singlet-A	1.9249 eV	644.11 nm	f=0.0341 <S**2>=0.000
203 -> 204	-0.12550			
203 -> 205	0.69249			
Excited State 3:	Singlet-A	2.9730 eV	417.04 nm	f=0.0314 <S**2>=0.000
201 -> 204	0.17773			
201 -> 205	0.16081			
202 -> 204	0.63948			
202 -> 205	0.17678			
Excited State 4:	Singlet-A	2.9943 eV	414.07 nm	f=0.1066 <S**2>=0.000
201 -> 205	-0.12173			
202 -> 204	-0.15748			
202 -> 205	0.66662			
203 -> 206	0.10845			
Excited State 5:	Singlet-A	3.0222 eV	410.24 nm	f=0.1526 <S**2>=0.000
201 -> 204	0.62294			
201 -> 205	-0.20393			
202 -> 204	-0.11030			
203 -> 206	-0.22618			
Excited State 6:	Singlet-A	3.1096 eV	398.71 nm	f=0.1194 <S**2>=0.000
201 -> 204	0.18147			
201 -> 205	0.63643			
202 -> 204	-0.22047			
Excited State 7:	Singlet-A	3.2302 eV	383.82 nm	f=0.0550 <S**2>=0.000
201 -> 204	0.16927			
203 -> 206	0.52433			
203 -> 207	0.26201			
203 -> 208	-0.31701			
Excited State 8:	Singlet-A	3.2989 eV	375.84 nm	f=0.0106 <S**2>=0.000
203 -> 206	-0.12843			
203 -> 207	0.63353			
203 -> 208	0.26479			
Excited State 9:	Singlet-A	3.4323 eV	361.23 nm	f=0.1003 <S**2>=0.000

203 -> 206	0.34031	
203 -> 207	-0.15024	
203 -> 208	0.55972	
203 -> 211	0.11072	
 Excited State 10:	Singlet-A	3.7293 eV 332.46 nm f=0.0058 <S**2>=0.000
203 -> 209	0.39671	
203 -> 211	0.55731	
 Excited State 11:	Singlet-A	3.7683 eV 329.02 nm f=0.0104 <S**2>=0.000
203 -> 209	0.55209	
203 -> 211	-0.37677	
 Excited State 12:	Singlet-A	3.7810 eV 327.91 nm f=0.0002 <S**2>=0.000
199 -> 204	-0.25706	
199 -> 205	-0.15717	
200 -> 204	-0.11607	
200 -> 205	0.16173	
201 -> 207	-0.20508	
202 -> 206	0.51315	
202 -> 208	-0.11817	
203 -> 209	-0.17281	
 Excited State 13:	Singlet-A	3.8140 eV 325.08 nm f=0.0107 <S**2>=0.000
199 -> 204	-0.26752	
199 -> 205	-0.15337	
200 -> 204	0.19757	
200 -> 205	-0.29106	
201 -> 206	-0.29708	
201 -> 208	0.21342	
202 -> 206	-0.11632	
202 -> 207	0.30109	
202 -> 208	0.10768	
203 -> 210	0.10804	
 Excited State 14:	Singlet-A	3.8930 eV 318.48 nm f=0.0117 <S**2>=0.000
200 -> 204	-0.12992	
200 -> 205	0.17305	
202 -> 206	-0.19273	
202 -> 208	-0.18882	
203 -> 210	0.58094	
 Excited State 15:	Singlet-A	3.8958 eV 318.25 nm f=0.0023 <S**2>=0.000
199 -> 204	0.20170	
199 -> 205	0.11824	
200 -> 204	0.12018	
200 -> 205	-0.17198	
201 -> 207	0.21319	
202 -> 206	0.39401	
202 -> 208	0.25484	
203 -> 210	0.33124	
 Excited State 16:	Singlet-A	3.9852 eV 311.11 nm f=0.0280 <S**2>=0.000
199 -> 204	-0.10670	
200 -> 205	-0.10260	
201 -> 206	0.60803	
201 -> 208	0.17071	
202 -> 207	0.15429	
203 -> 210	0.13444	
 Excited State 17:	Singlet-A	4.1568 eV 298.27 nm f=0.0053 <S**2>=0.000
198 -> 204	0.65630	
198 -> 205	-0.20020	
200 -> 204	-0.10508	
 Excited State 18:	Singlet-A	4.2069 eV 294.72 nm f=0.0134 <S**2>=0.000
198 -> 204	0.17093	

198 -> 205	0.63294	
200 -> 204	-0.16935	
200 -> 205	-0.15221	
 Excited State 19:	Singlet-A	4.2299 eV 293.12 nm f=0.0008 <S**2>=0.000
198 -> 204	0.14189	
198 -> 205	0.19507	
200 -> 204	0.55635	
200 -> 205	0.35192	
 Excited State 20:	Singlet-A	4.2424 eV 292.25 nm f=0.0057 <S**2>=0.000
203 -> 212	0.68839	
 Excited State 21:	Singlet-A	4.2786 eV 289.77 nm f=0.0018 <S**2>=0.000
199 -> 204	-0.37809	
199 -> 205	0.59402	
 Excited State 22:	Singlet-A	4.3854 eV 282.72 nm f=0.0029 <S**2>=0.000
196 -> 205	-0.15760	
197 -> 204	0.26505	
197 -> 205	-0.32181	
201 -> 207	0.28564	
201 -> 208	-0.14442	
202 -> 207	0.33646	
202 -> 208	-0.19079	
202 -> 209	-0.10101	
 Excited State 23:	Singlet-A	4.4093 eV 281.19 nm f=0.0059 <S**2>=0.000
196 -> 204	-0.16649	
196 -> 205	-0.24338	
197 -> 204	0.42282	
197 -> 205	-0.13415	
201 -> 207	-0.18068	
201 -> 208	0.17530	
201 -> 209	-0.12945	
202 -> 207	-0.30441	
202 -> 208	0.11798	
202 -> 210	0.12711	
 Excited State 24:	Singlet-A	4.4166 eV 280.72 nm f=0.0029 <S**2>=0.000
196 -> 204	0.40522	
197 -> 205	-0.37402	
201 -> 207	-0.22544	
201 -> 210	0.12274	
202 -> 207	-0.11546	
202 -> 208	0.19007	
202 -> 209	-0.17620	
 Excited State 25:	Singlet-A	4.4566 eV 278.21 nm f=0.0135 <S**2>=0.000
196 -> 204	0.12342	
201 -> 207	0.22735	
201 -> 208	0.45688	
202 -> 207	-0.22894	
202 -> 208	-0.38355	
 Excited State 26:	Singlet-A	4.4835 eV 276.53 nm f=0.0297 <S**2>=0.000
203 -> 213	0.55213	
203 -> 214	0.35257	
203 -> 215	0.10451	
203 -> 218	0.13086	
 Excited State 27:	Singlet-A	4.6207 eV 268.32 nm f=0.0027 <S**2>=0.000
196 -> 204	0.36673	
196 -> 205	0.19626	
197 -> 204	0.43002	
197 -> 205	0.33959	
201 -> 209	0.10066	

```

Excited State 28:      Singlet-A      4.6398 eV  267.22 nm  f=0.0510  <S**2>=0.000
  194 -> 204      0.14240
  194 -> 205      0.13396
  195 -> 204      0.39066
  195 -> 205     -0.14986
  196 -> 204     -0.11225
  202 -> 209     -0.18022
  203 -> 213      0.25487
  203 -> 214     -0.34317

Excited State 29:      Singlet-A      4.6521 eV  266.51 nm  f=0.0231  <S**2>=0.000
  194 -> 204      0.10743
  195 -> 204      0.45217
  195 -> 205     -0.17778
  202 -> 209      0.10571
  203 -> 213     -0.27089
  203 -> 214      0.33914

Excited State 30:      Singlet-A      4.6676 eV  265.63 nm  f=0.0062  <S**2>=0.000
  194 -> 204      0.37538
  195 -> 205      0.48126
  196 -> 204     -0.18555
  196 -> 205      0.17133
  197 -> 205     -0.12971
  201 -> 209      0.10080
  202 -> 211     -0.11074

Excited State 31:      Singlet-A      4.6746 eV  265.23 nm  f=0.0003  <S**2>=0.000
  194 -> 204     -0.14701
  195 -> 205     -0.23815
  196 -> 204     -0.23918
  196 -> 205      0.51752
  197 -> 204      0.14919
  197 -> 205     -0.19953

Excited State 32:      Singlet-A      4.7238 eV  262.47 nm  f=0.0808  <S**2>=0.000
  194 -> 204      0.13006
  194 -> 205     -0.14419
  195 -> 205     -0.14156
  196 -> 205     -0.11613
  199 -> 204     -0.15048
  199 -> 205     -0.10999
  200 -> 204     -0.12242
  200 -> 205      0.20198
  201 -> 207      0.24035
  201 -> 209      0.15940
  202 -> 208      0.22759
  202 -> 210     -0.16576
  203 -> 215      0.32085
  203 -> 216      0.14044

```

JOB name: ti552Ant2TD
Method/Basis: TD-B3LYP-D3/6-311G(d) [hexane]

Table S5. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of 8

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Excited State 1:      Singlet-A      2.2210 eV  558.24 nm  f=0.0181  <S**2>=0.000
  260 -> 263     -0.27062
  261 -> 262      0.65165

```

Excited State	2:	Singlet-A	2.3184 eV	534.78 nm	f=0.0034 <S**2>=0.000
	260 -> 262	0.58675			
	261 -> 263	-0.39196			
Excited State	3:	Singlet-A	2.8261 eV	438.71 nm	f=0.4257 <S**2>=0.000
	260 -> 262	0.39217			
	261 -> 263	0.58535			
Excited State	4:	Singlet-A	3.0058 eV	412.48 nm	f=0.1538 <S**2>=0.000
	260 -> 263	0.64538			
	261 -> 262	0.26327			
Excited State	5:	Singlet-A	3.5651 eV	347.77 nm	f=0.0020 <S**2>=0.000
	261 -> 264	0.69620			
Excited State	6:	Singlet-A	3.7556 eV	330.13 nm	f=0.0022 <S**2>=0.000
	260 -> 264	0.68038			
	261 -> 265	0.16167			
Excited State	7:	Singlet-A	3.9780 eV	311.68 nm	f=0.0003 <S**2>=0.000
	259 -> 262	0.22513			
	260 -> 264	-0.14284			
	260 -> 266	0.26120			
	261 -> 265	0.58813			
Excited State	8:	Singlet-A	4.0275 eV	307.84 nm	f=0.0187 <S**2>=0.000
	260 -> 265	0.41005			
	261 -> 266	0.54771			
Excited State	9:	Singlet-A	4.0979 eV	302.55 nm	f=0.0094 <S**2>=0.000
	258 -> 263	0.21916			
	259 -> 262	0.60887			
	260 -> 264	0.10946			
	261 -> 265	-0.21528			
Excited State	10:	Singlet-A	4.1588 eV	298.13 nm	f=0.0061 <S**2>=0.000
	257 -> 263	0.10577			
	258 -> 262	0.60406			
	259 -> 263	0.31955			
Excited State	11:	Singlet-A	4.3403 eV	285.66 nm	f=0.0294 <S**2>=0.000
	259 -> 263	0.18493			
	260 -> 265	0.52452			
	261 -> 266	-0.40439			
Excited State	12:	Singlet-A	4.3427 eV	285.50 nm	f=0.0104 <S**2>=0.000
	260 -> 266	0.62606			
	261 -> 265	-0.25567			
	261 -> 267	-0.10144			
Excited State	13:	Singlet-A	4.3837 eV	282.83 nm	f=0.0051 <S**2>=0.000
	256 -> 263	0.10980			
	257 -> 262	0.65098			
	258 -> 263	0.18694			
	259 -> 262	-0.11519			
Excited State	14:	Singlet-A	4.4168 eV	280.71 nm	f=0.0182 <S**2>=0.000
	256 -> 262	-0.13986			
	257 -> 263	-0.11815			

258 -> 262	-0.31047	
259 -> 263	0.57226	
260 -> 265	-0.16077	
 Excited State 15:	Singlet-A	4.5385 eV 273.18 nm f=0.0107 <S**2>=0.000
260 -> 268	-0.12687	
261 -> 267	0.66650	
261 -> 269	0.10850	
 Excited State 16:	Singlet-A	4.6088 eV 269.01 nm f=0.0471 <S**2>=0.000
256 -> 262	0.44374	
257 -> 263	0.33222	
258 -> 262	-0.14895	
259 -> 263	0.10428	
260 -> 267	0.13862	
260 -> 270	0.10429	
261 -> 268	-0.30249	
 Excited State 17:	Singlet-A	4.6213 eV 268.29 nm f=0.0112 <S**2>=0.000
257 -> 262	-0.21873	
258 -> 263	0.60799	
259 -> 262	-0.18392	
261 -> 269	0.11247	
 Excited State 18:	Singlet-A	4.6609 eV 266.01 nm f=0.0094 <S**2>=0.000
256 -> 262	0.30261	
257 -> 263	0.18351	
260 -> 267	-0.34830	
260 -> 270	-0.12522	
261 -> 268	0.45250	
 Excited State 19:	Singlet-A	4.7137 eV 263.03 nm f=0.0000 <S**2>=0.000
258 -> 263	-0.16327	
260 -> 268	-0.20607	
260 -> 271	-0.11621	
261 -> 267	-0.16546	
261 -> 269	0.51387	
261 -> 270	0.32268	
 Excited State 20:	Singlet-A	4.7540 eV 260.80 nm f=0.0359 <S**2>=0.000
256 -> 262	0.19620	
257 -> 263	-0.12549	
260 -> 267	0.53042	
261 -> 268	0.27408	
261 -> 271	0.24895	
 Excited State 21:	Singlet-A	4.7814 eV 259.31 nm f=0.0115 <S**2>=0.000
254 -> 262	-0.11504	
256 -> 262	-0.36017	
257 -> 263	0.53598	
260 -> 267	0.15726	
261 -> 268	0.14410	
 Excited State 22:	Singlet-A	4.8180 eV 257.34 nm f=0.0335 <S**2>=0.000
255 -> 262	-0.12380	
260 -> 268	0.32251	
260 -> 271	0.10155	
261 -> 269	0.41725	
261 -> 270	-0.37664	
261 -> 276	0.12597	

Excited State 23: Singlet-A 4.8680 eV 254.69 nm f=0.0012 <S**2>=0.000
 255 -> 262 0.62836
 256 -> 263 0.20553
 261 -> 269 0.10406

Excited State 24: Singlet-A 4.8934 eV 253.37 nm f=0.0282 <S**2>=0.000
 254 -> 262 0.58914
 255 -> 263 0.16304
 257 -> 263 0.13258
 260 -> 269 -0.26805

Excited State 25: Singlet-A 4.9039 eV 252.83 nm f=0.0002 <S**2>=0.000
 253 -> 262 0.45003
 254 -> 263 -0.12750
 255 -> 262 -0.21694
 256 -> 263 0.44865

Excited State 26: Singlet-A 4.9333 eV 251.32 nm f=0.0205 <S**2>=0.000
 254 -> 262 0.28893
 260 -> 269 0.55122
 260 -> 270 0.21557
 261 -> 268 0.15520
 261 -> 271 -0.11988

Excited State 27: Singlet-A 4.9577 eV 250.08 nm f=0.0004 <S**2>=0.000
 260 -> 267 -0.18024
 260 -> 269 0.16770
 261 -> 266 -0.10810
 261 -> 268 -0.23193
 261 -> 271 0.56650

Excited State 28: Singlet-A 4.9598 eV 249.98 nm f=0.0044 <S**2>=0.000
 260 -> 268 0.51424
 260 -> 271 0.10416
 261 -> 270 0.43774

Excited State 29: Singlet-A 5.0580 eV 245.12 nm f=0.0016 <S**2>=0.000
 260 -> 269 -0.17809
 260 -> 270 0.56016
 261 -> 271 0.11448
 261 -> 272 0.28494
 261 -> 274 0.14955

Excited State 30: Singlet-A 5.0696 eV 244.56 nm f=0.0008 <S**2>=0.000
 251 -> 262 -0.13771
 253 -> 262 -0.46213
 256 -> 263 0.47186

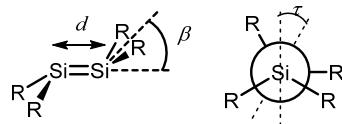
Excited State 31: Singlet-A 5.0975 eV 243.23 nm f=0.0027 <S**2>=0.000
 260 -> 270 -0.22995
 260 -> 275 0.10281
 261 -> 271 -0.19883
 261 -> 272 0.60748

Excited State 32: Singlet-A 5.1147 eV 242.41 nm f=0.0013 <S**2>=0.000
 260 -> 266 -0.10534
 260 -> 268 -0.16651
 260 -> 271 0.55044
 260 -> 272 0.12605

261 -> 273 0.30040
 261 -> 276 0.16433

JOB name: ti552butadieneTD
 Method/Basis: TD-B3LYP-D3/6-311G(d) [hexane]

Table S6. Selected Parameters



Cpd	d/Å	angle sum at Si/°	β/°	τ/°
1 (XRD)	2.1762(5)	358.52(3) (<i>Si1</i> -SiMe ₃), 359.61(3) (<i>Si2</i> -SiMe ₃)	12.9 (<i>Si1</i> -SiMe ₃), 6.5 (<i>Si2</i> -SiMe ₃)	17.7
1 (calcd) ^a	2.17640	358.58, 358.58	12.6 (<i>Si1</i>), 12.6 (<i>Si1</i>)	12.9
4 (XRD)	2.2035(5)	358.04(3) (= <i>Si</i> ···K), 359.94(3) (= <i>Si</i> -SiMe ₃)	3.7 (= <i>Si</i> ···K), 1.5 (= <i>Si</i> -SiMe ₃)	2.5
5 (XRD)	2.1860(19)	358.8(1) (= <i>Si</i> -SiEt ₃), 358.6(1) (= <i>Si</i> -SiMe ₃)	11.2 (= <i>Si</i> -SiEt ₃), 12.1 (= <i>Si</i> -SiMe ₃)	17.6
6 (XRD)	2.1598(6)	360.00(5) (= <i>Si</i> -Ant), 355.98(3) (= <i>Si</i> -SiMe ₃)	0.1 (= <i>Si</i> -Ant), 22.5 (= <i>Si</i> -SiMe ₃)	0.1
6 (calcd) ^a	2.15862	358.25 (= <i>Si</i> -Ant), 354.93 (= <i>Si</i> -SiMe ₃)	12.9 (= <i>Si</i> -Ant), 25.3 (= <i>Si</i> -SiMe ₃)	3.7
6^{Br} (XRD)	2.1711(7)	359.76(6) (= <i>Si</i> -Ant ^{Br}), 356.04(5) (= <i>Si</i> -SiMe ₃)	4.7 (= <i>Si</i> -Ant ^{Br}), 22.4 (= <i>Si</i> -SiMe ₃)	8.5
6^{Br} (calcd) ^a	2.1574	358.25 (= <i>Si</i> -Ant ^{Br}), 354.93 (= <i>Si</i> -SiMe ₃)	12.1 (= <i>Si</i> -Ant ^{Br}), 25.3 (= <i>Si</i> -SiMe ₃)	3.7
7 (XRD)	2.1525(7)	357.10(6) (<i>Si1</i> -Ant), 355.71(6) (<i>Si2</i> -Ant)	17.4 (= <i>Si1</i> -Ant), 21.0 (= <i>Si2</i> -Ant)	3.3
7 (calcd) ^a	2.1440	356.42 (<i>Si1</i> -Ant), 358.43 (<i>Si2</i> -Ant)	19.1 (= <i>Si1</i> -Ant), 12.8 (= <i>Si2</i> -Ant)	2.8
8 (XRD)	2.1850(4) (<i>Si1</i> = <i>Si2</i>) 2.1915(5) (<i>Si3</i> = <i>Si4</i>)	359.99(4) (<i>Si1</i>), 359.99(3) (<i>Si2</i>), 359.98(3) (<i>Si3</i>), 359.94(4) (<i>Si4</i>)	0.3 (<i>Si1</i>), 1.2 (<i>Si2</i>), 1.0 (<i>Si3</i>), 2.4 (<i>Si4</i>)	0.7 (<i>Si1</i> = <i>Si2</i>), 1.8 (<i>Si3</i> = <i>Si4</i>) [-88.36(2)° (<i>Si1</i> - <i>Si2</i> - <i>Si3</i> - <i>Si4</i>)]
8 (calcd) ^a	2.1907, 2.1904	359.33 (<i>Si1</i>), 359.04 (<i>Si2</i>), 359.10 (<i>Si3</i>), 358.39 (<i>Si4</i>)	13.6 (<i>Si1</i>), 10.5 (<i>Si2</i>), 10.3 (<i>Si3</i>), 13.3 (<i>Si4</i>)	3.9 (<i>Si1</i> = <i>Si2</i>), 3.9 (<i>Si3</i> = <i>Si4</i>), [-71.4° (<i>Si1</i> - <i>Si2</i> - <i>Si3</i> - <i>Si4</i>)]

a. The geometry was optimized at the B3PW91-D3/6-31G(d) level of theory.

4. References

- S1. **Gaussian 09**, Revision E.01, Frisch, M. J.; Trucks, G. W.; Schlegel, H. B.; Scuseria, G. E.; Robb, M. A.; Cheeseman, J. R.; Scalmani, G.; Barone, V.; Mennucci, B.; Petersson, G. A.; Nakatsuji, H.; Caricato, M.; Li, X.; Hratchian, H. P.; Izmaylov, A. F.; Bloino, J.; Zheng, G.; Sonnenberg, J. L.; Hada, M.; Ehara, M.; Toyota, K.; Fukuda, R.; Hasegawa, J.; Ishida, M.; Nakajima, T.; Honda, Y.; Kitao, O.; Nakai, H.; Vreven, T.; Montgomery, J. A., Jr.; Peralta, J. E.; Ogliaro, F.; Bearpark, M.; Heyd, J. J.; Brothers, E.; Kudin, K. N.; Staroverov, V. N.; Kobayashi, R.; Normand, J.; Raghavachari, K.; Rendell, A.; Burant, J. C.; Iyengar, S. S.; Tomasi, J.; Cossi, M.; Rega, N.; Millam, J. M.; Klene, M.; Knox, J. E.; Cross, J. B.; Bakken, V.; Adamo, C.; Jaramillo, J.; Gomperts, R.; Stratmann, R. E.; Yazyev, O.; Austin, A. J.; Cammi, R.; Pomelli, C.; Ochterski, J. W.; Martin, R. L.; Morokuma, K.; Zakrzewski, V. G.; Voth, G. A.; Salvador, P.; Dannenberg, J. J.; Dapprich, S.; Daniels, A. D.; Farkas, Ö.; Foresman, J. B.; Ortiz, J. V.; Cioslowski, J.; Fox, D. J. Gaussian, Inc., Wallingford CT, 2009.
- S2. **GRRM14**, Maeda, S.; Harabuchi, Y.; Osada, Y.; Taketsugu, T.; Morokuma K.; Ohno, K.; see: <http://grrm.chem.tohoku.ac.jp/GRRM/>; Maeda, S.; Ohno, K.; Morokuma, K. *Phys. Chem. Chem. Phys.* **2013**, *15*, 3683-3701.